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**Yamada et al.**

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(54) **POWER CONVERSION APPARATUS HAVING AN AC/DC CONVERTER WHICH OUTPUTS TO A DC/DC CONVERTER WHICH IS CONTROLLED BY A CONTROLLER**

(58) **Field of Classification Search**  
USPC ..... 323/282–287; 363/44–48, 65, 67, 68, 363/71, 78, 79, 97, 98  
See application file for complete search history.

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(57) **ABSTRACT**

A power conversion apparatus includes a high-power-factor converter section converting an AC voltage to a DC voltage, a smoothing capacitor, a DC/DC converter section, and a control circuit. The control circuit controls the high-power-factor converter section such that the power factor of AC is controlled and a DC voltage follows a target value, and performs duty control for semiconductor switching devices such that a DC voltage from the DC/DC converter section to a load follows an instruction value. In accordance with the DC voltage, the control circuit adjusts the DC voltage target value of the high-power-factor converter section such that the duty ratio of the semiconductor switching devices approaches a set value, thereby optimizing the duty ratio of the semiconductor switching devices and reducing power loss.

**18 Claims, 23 Drawing Sheets**

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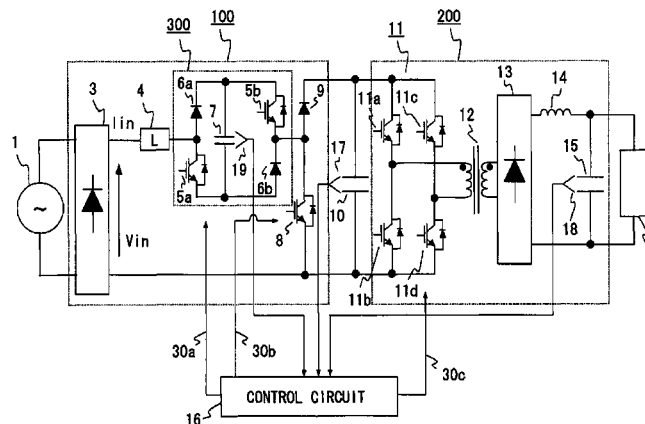
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**G05F 1/00** (2006.01)  
**H02M 7/217** (2006.01)  
**H02M 1/00** (2007.01)

(52) **U.S. Cl.**  
CPC ..... **H02M 7/217** (2013.01); **H02M 2001/007** (2013.01)



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FIG. 1

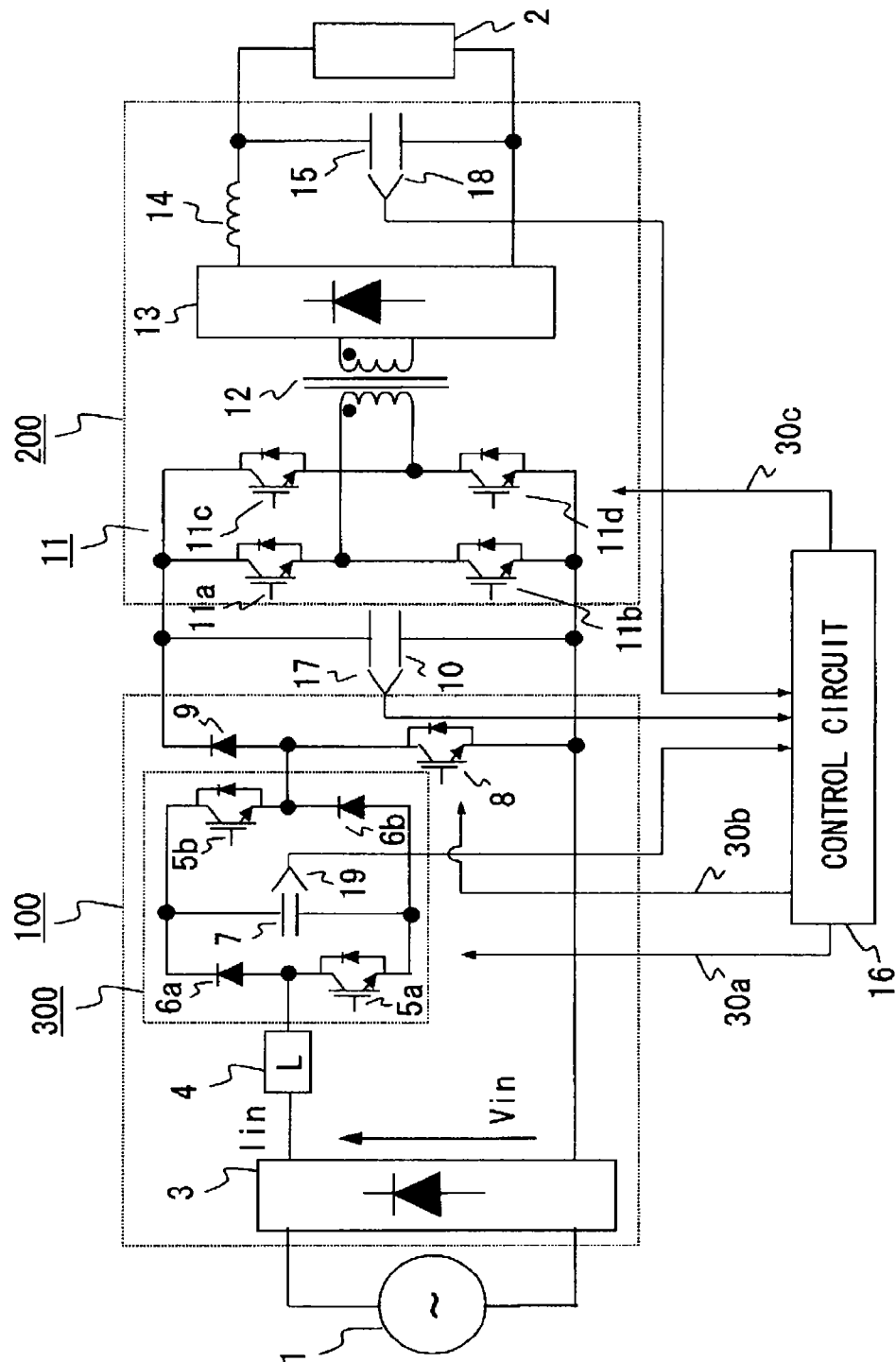


FIG. 2

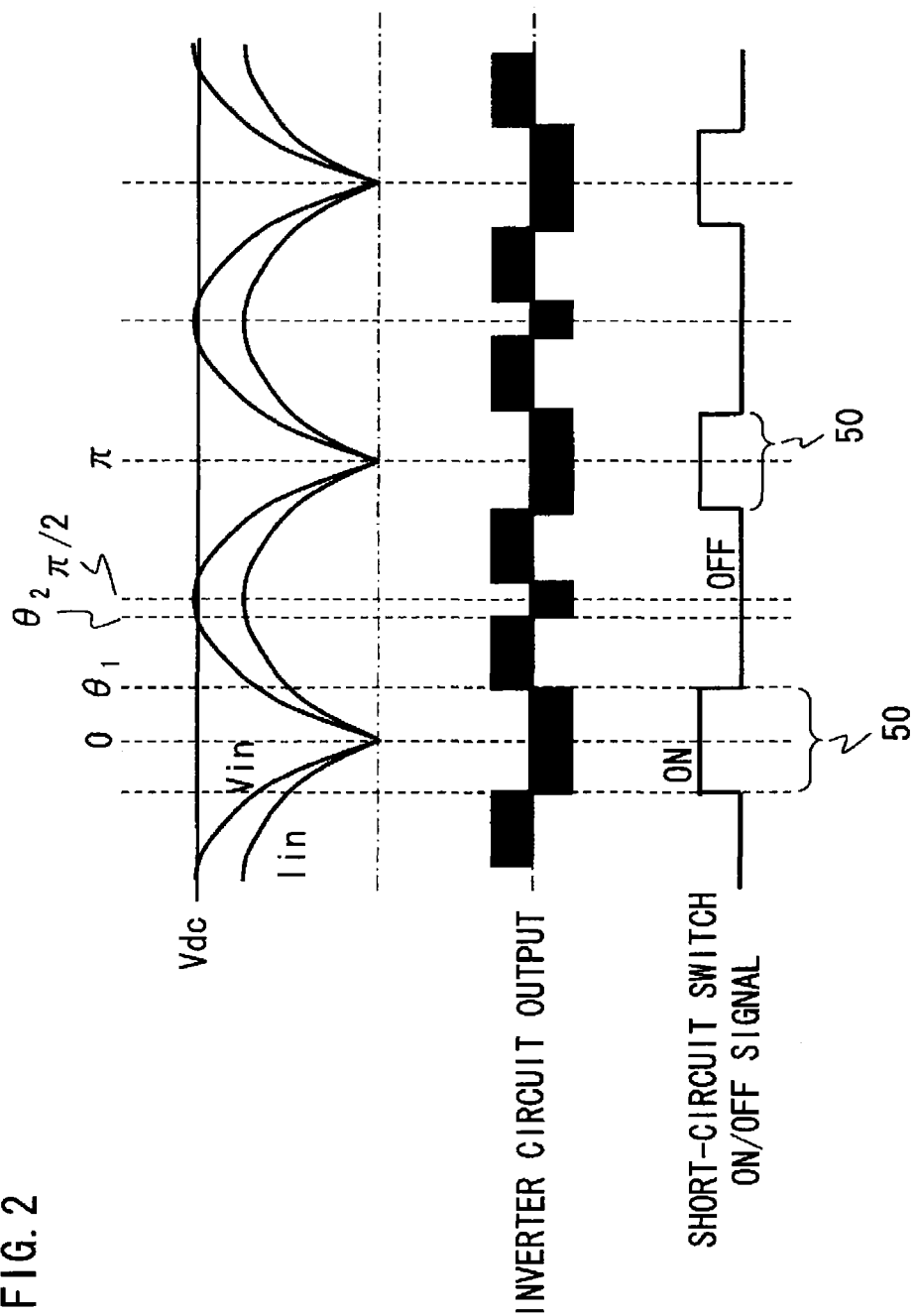


FIG. 3

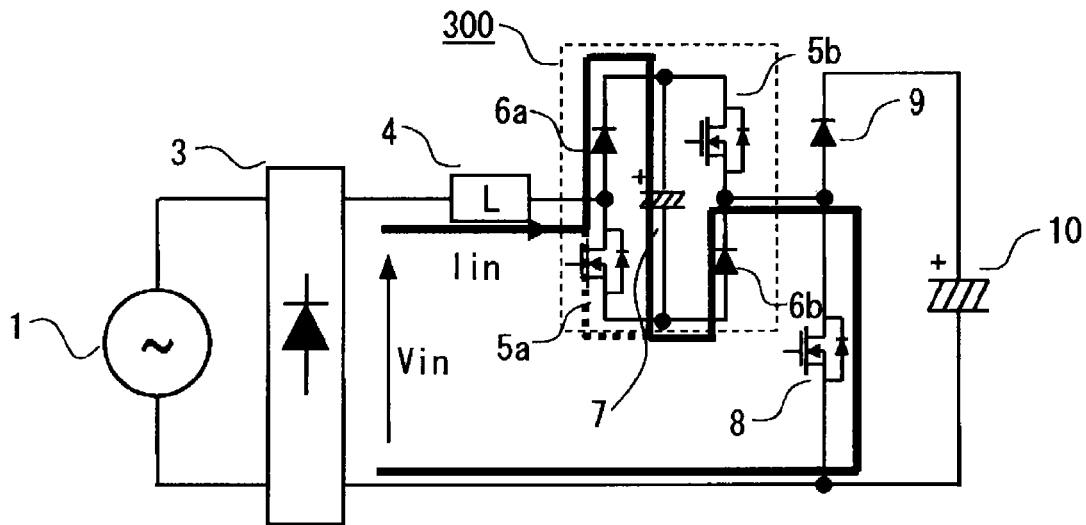


FIG. 4

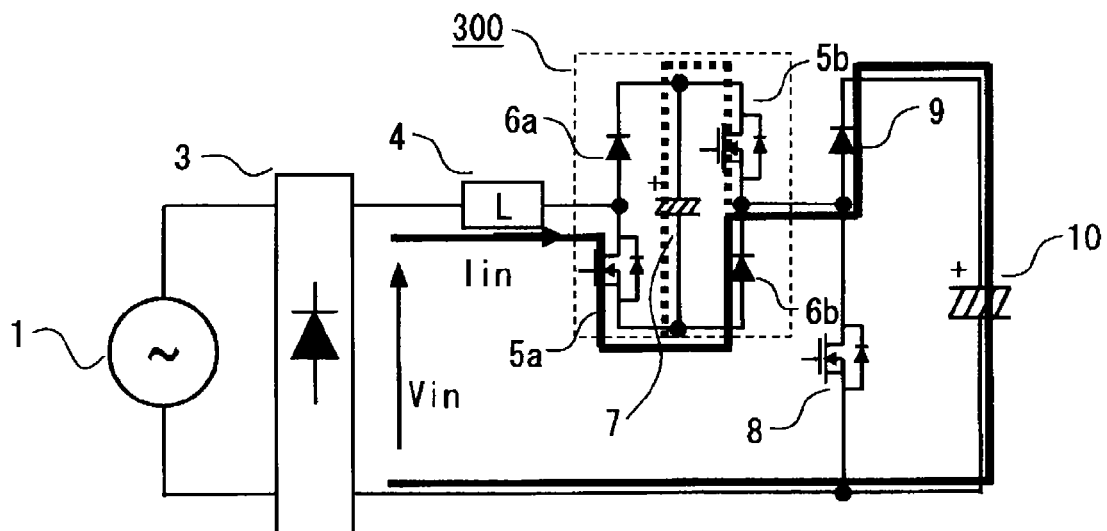


FIG. 5

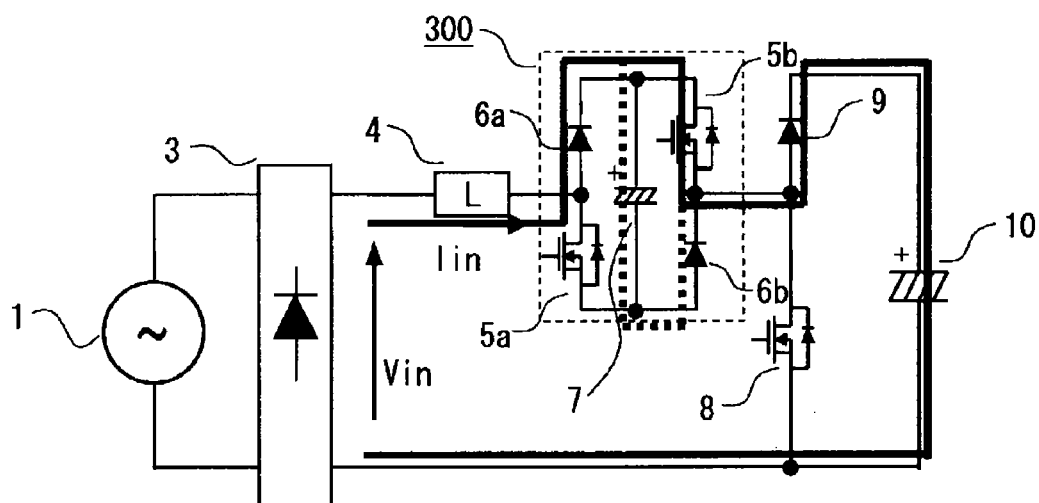


FIG. 6

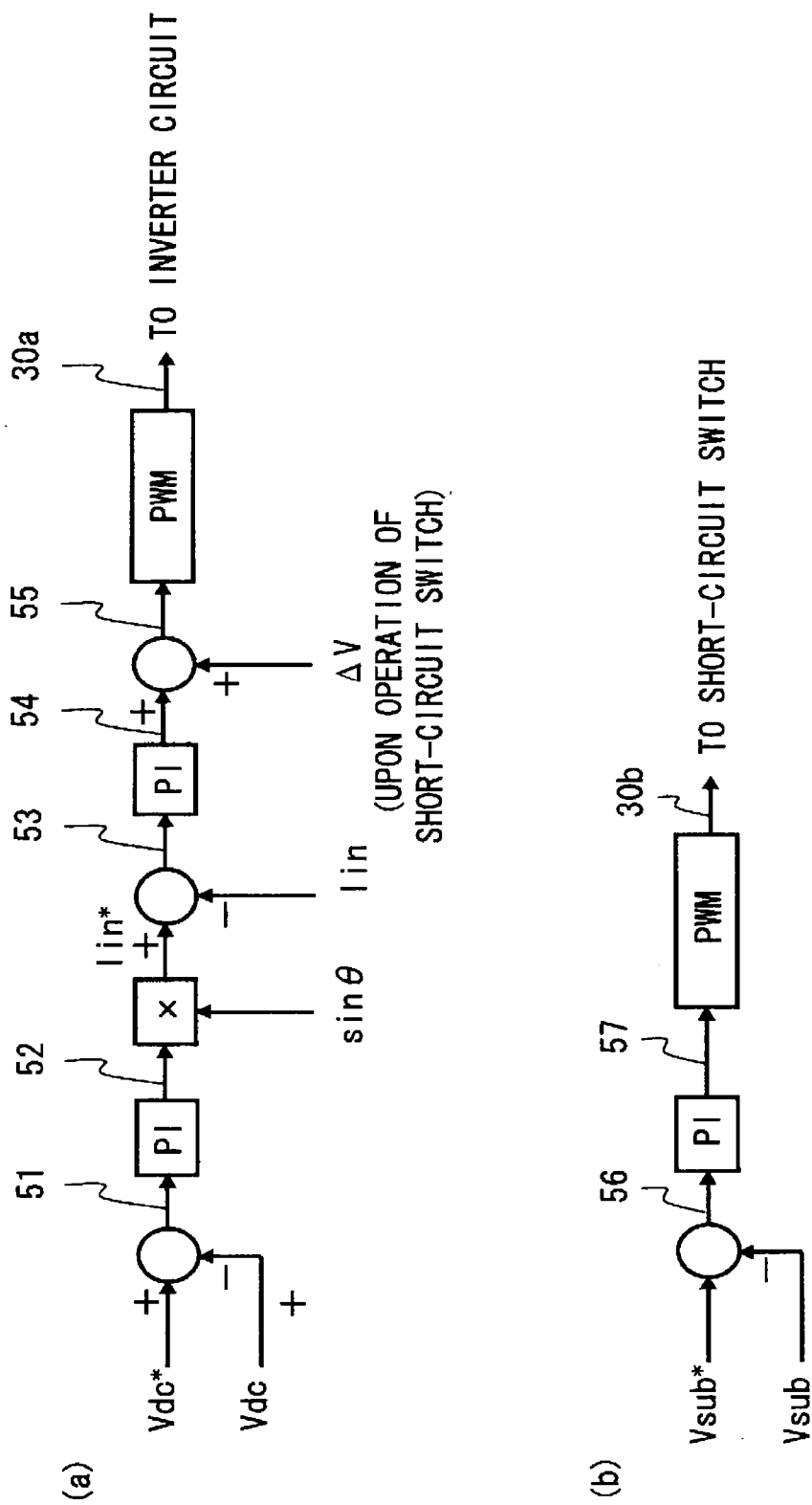


FIG. 7

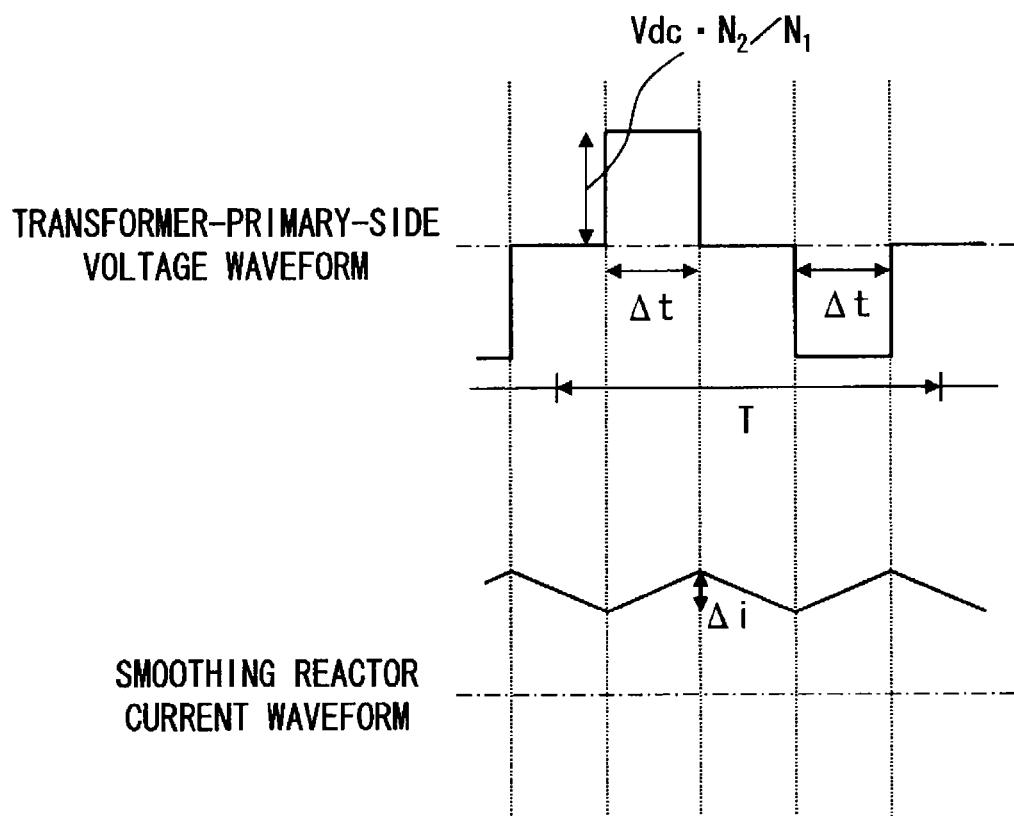




FIG. 8

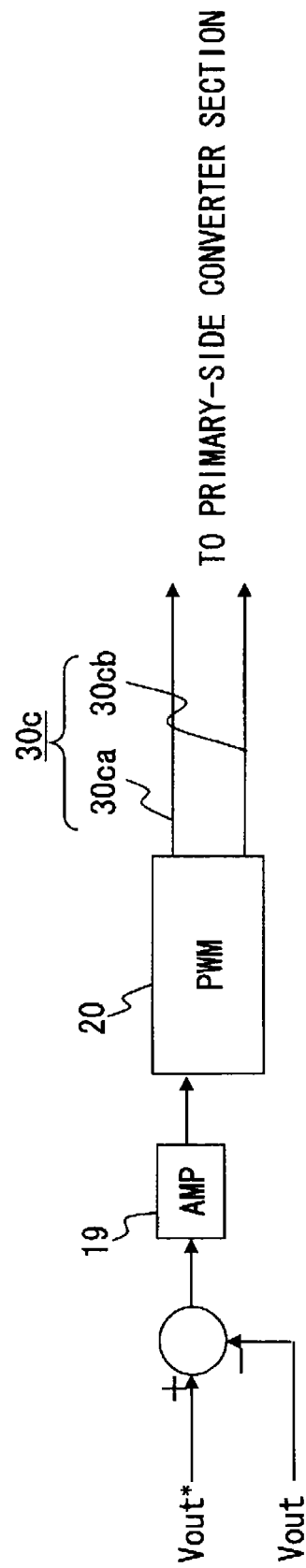


FIG. 9

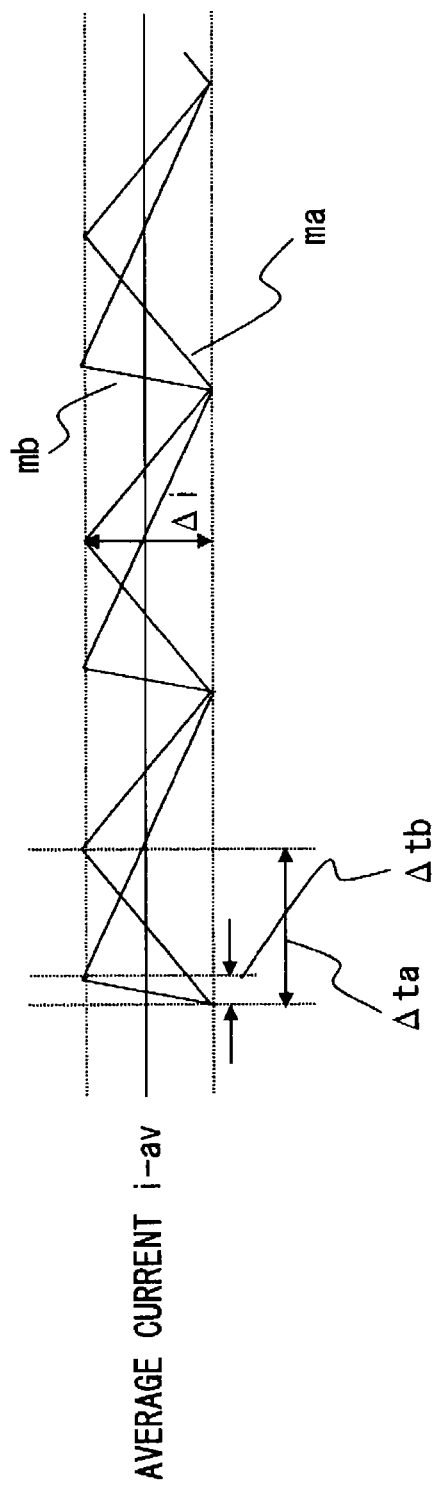


FIG. 10

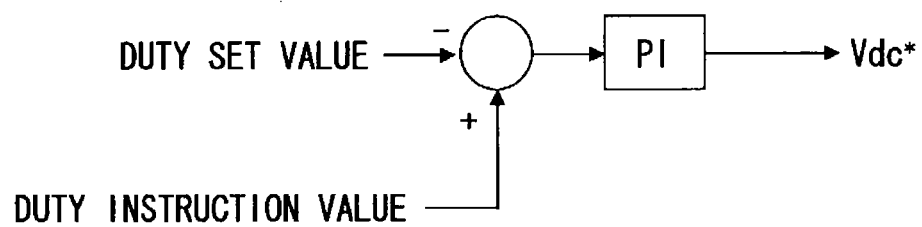


FIG. 11

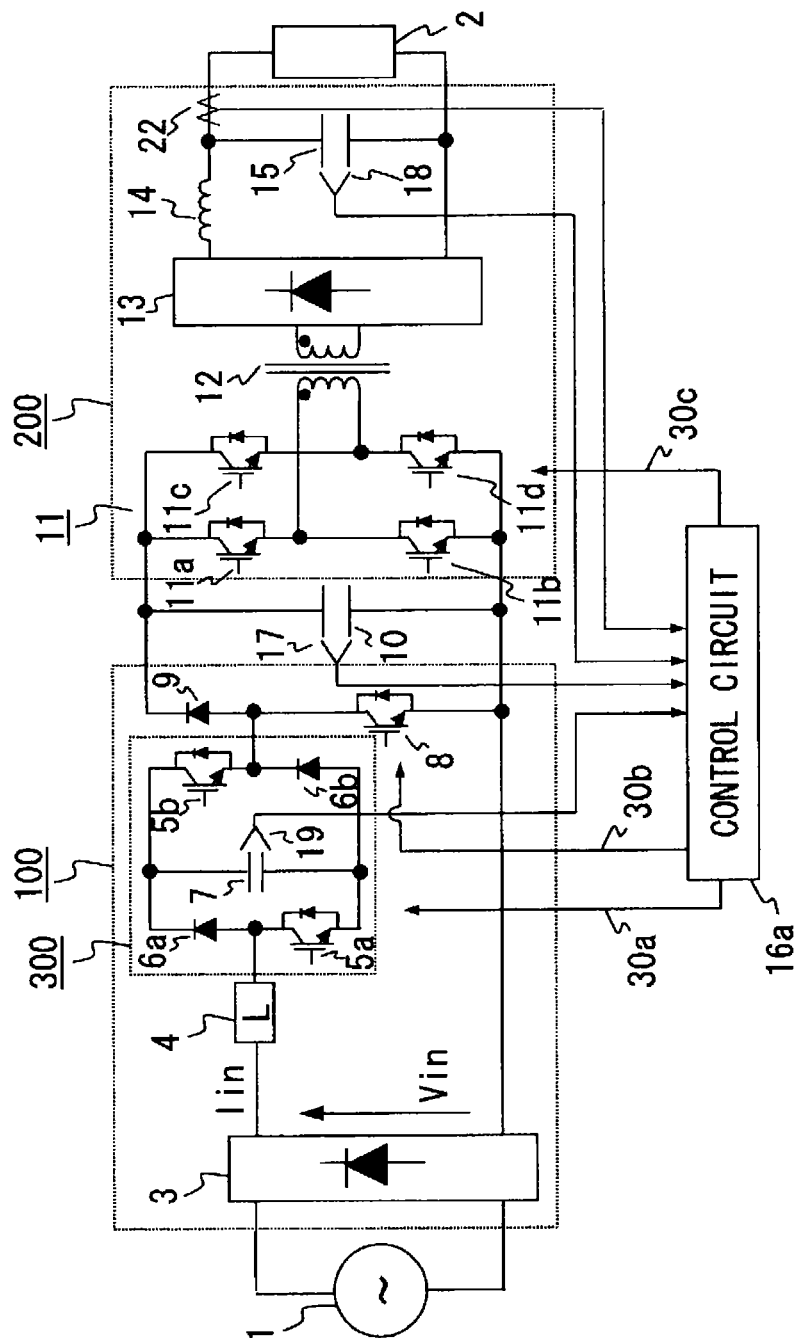


FIG. 12

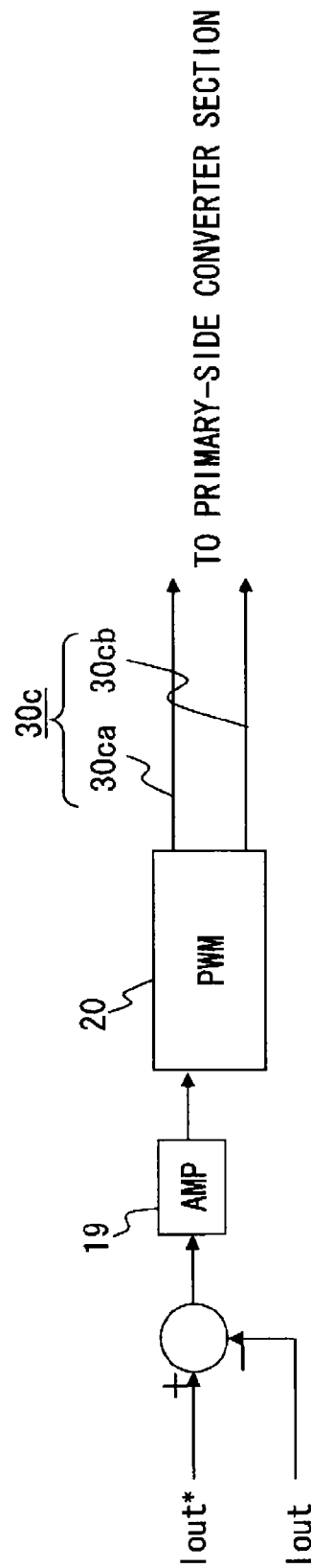


FIG. 13

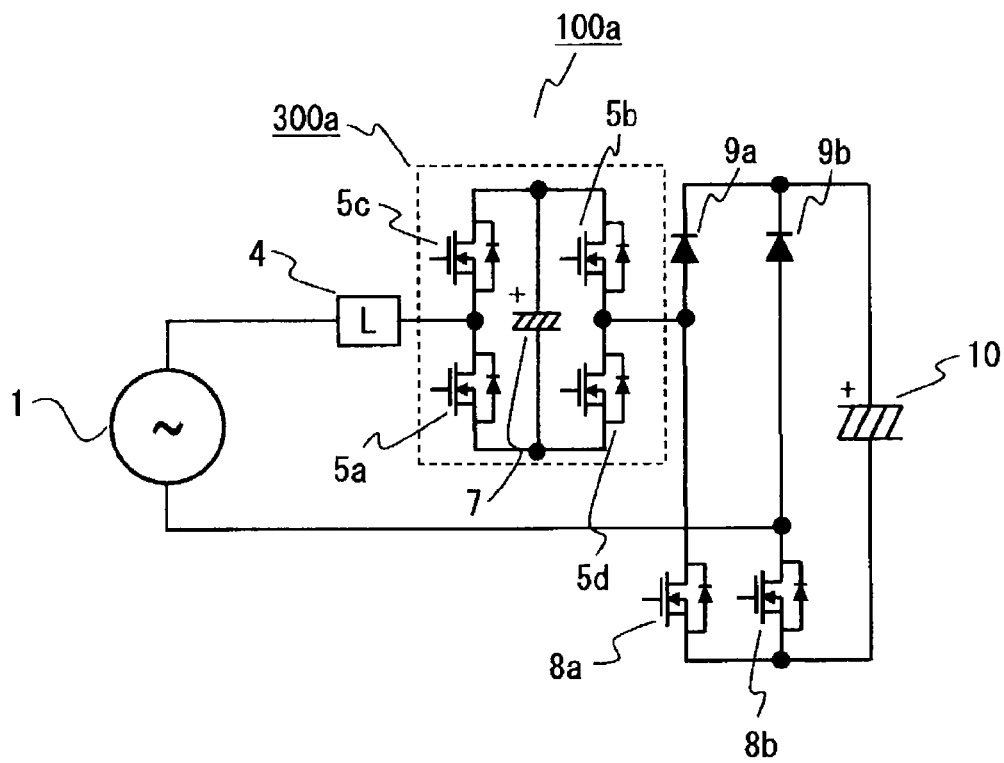


FIG. 14

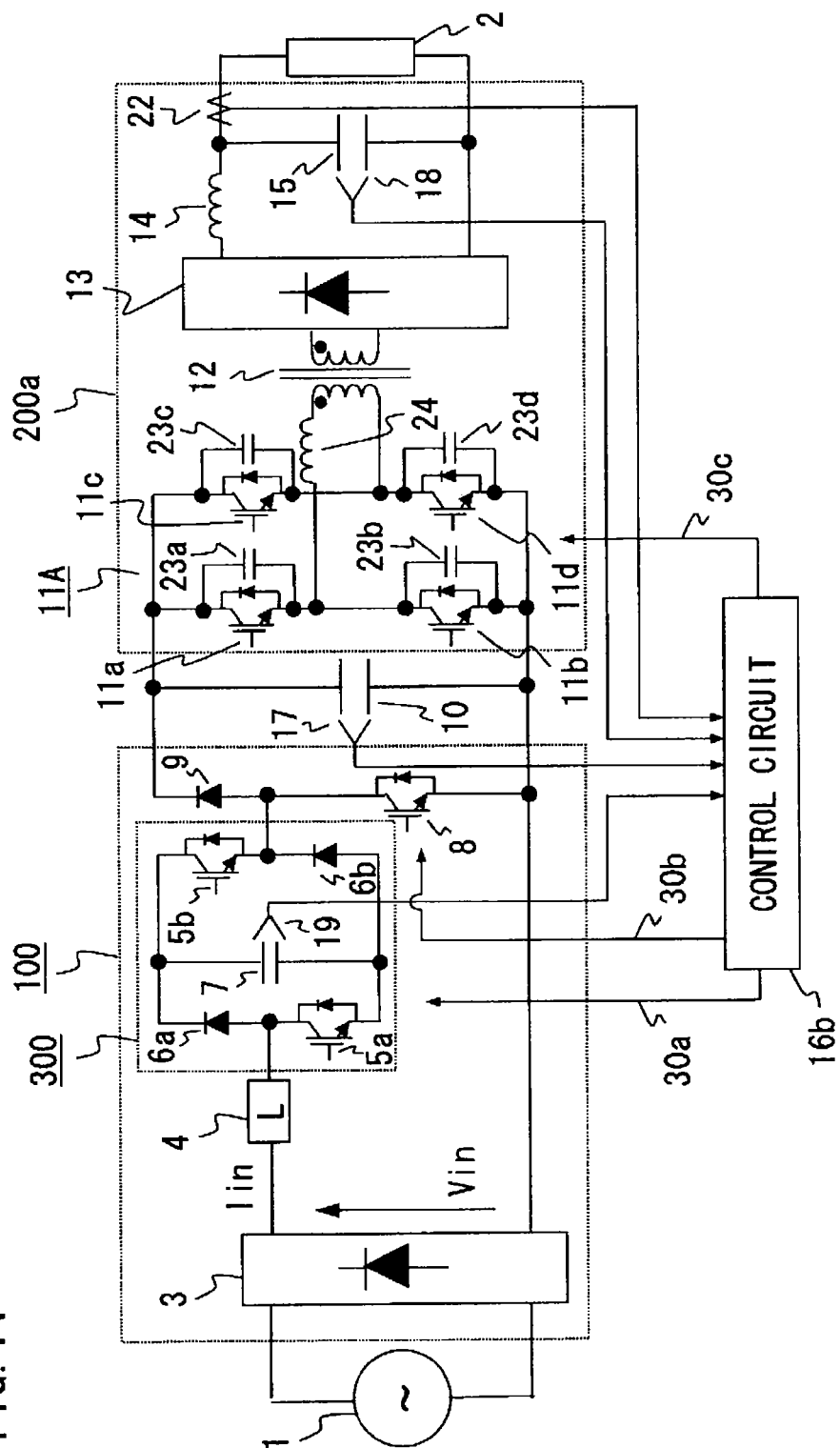


FIG. 15

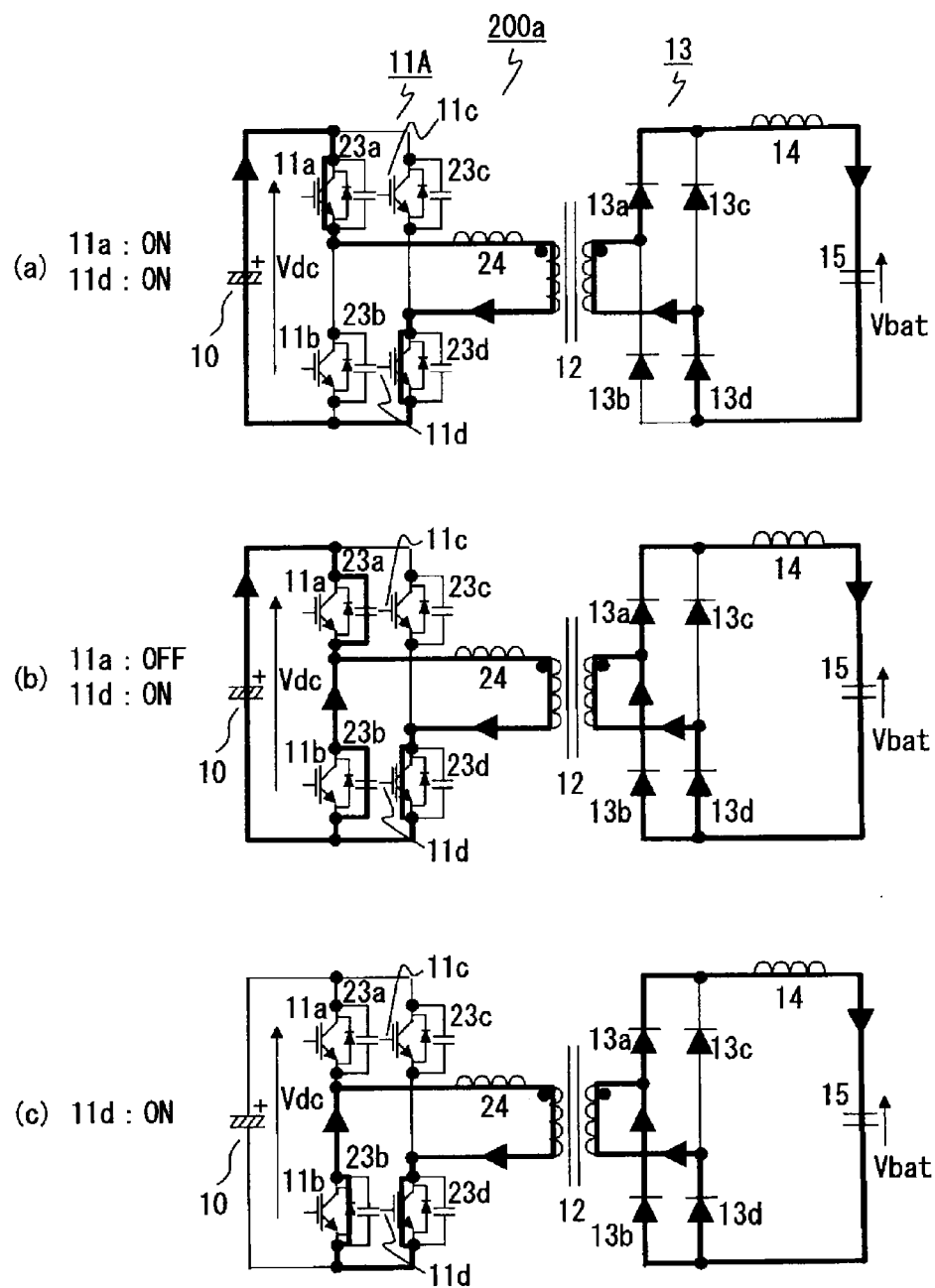




FIG. 16

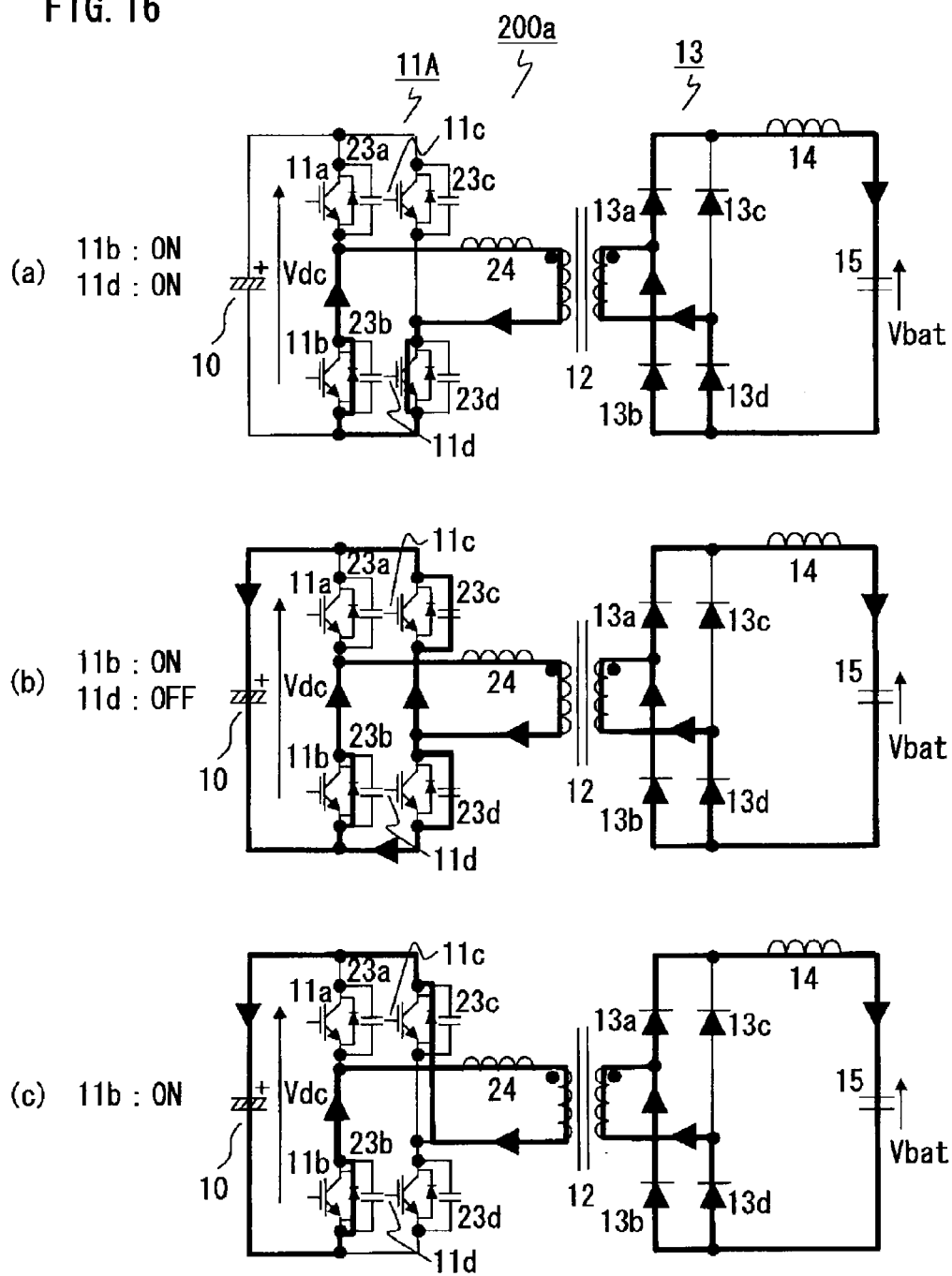


FIG. 17

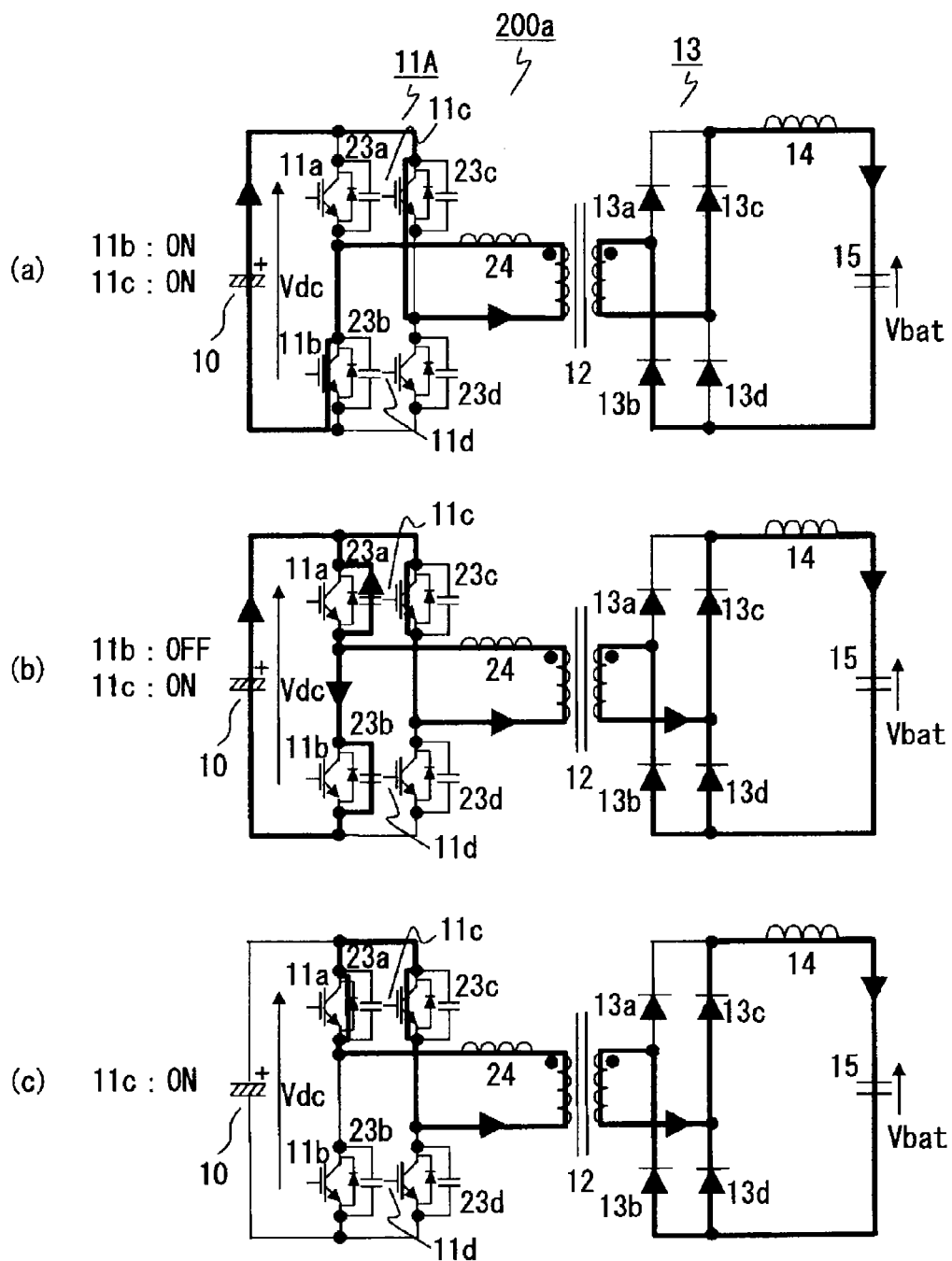


FIG. 18

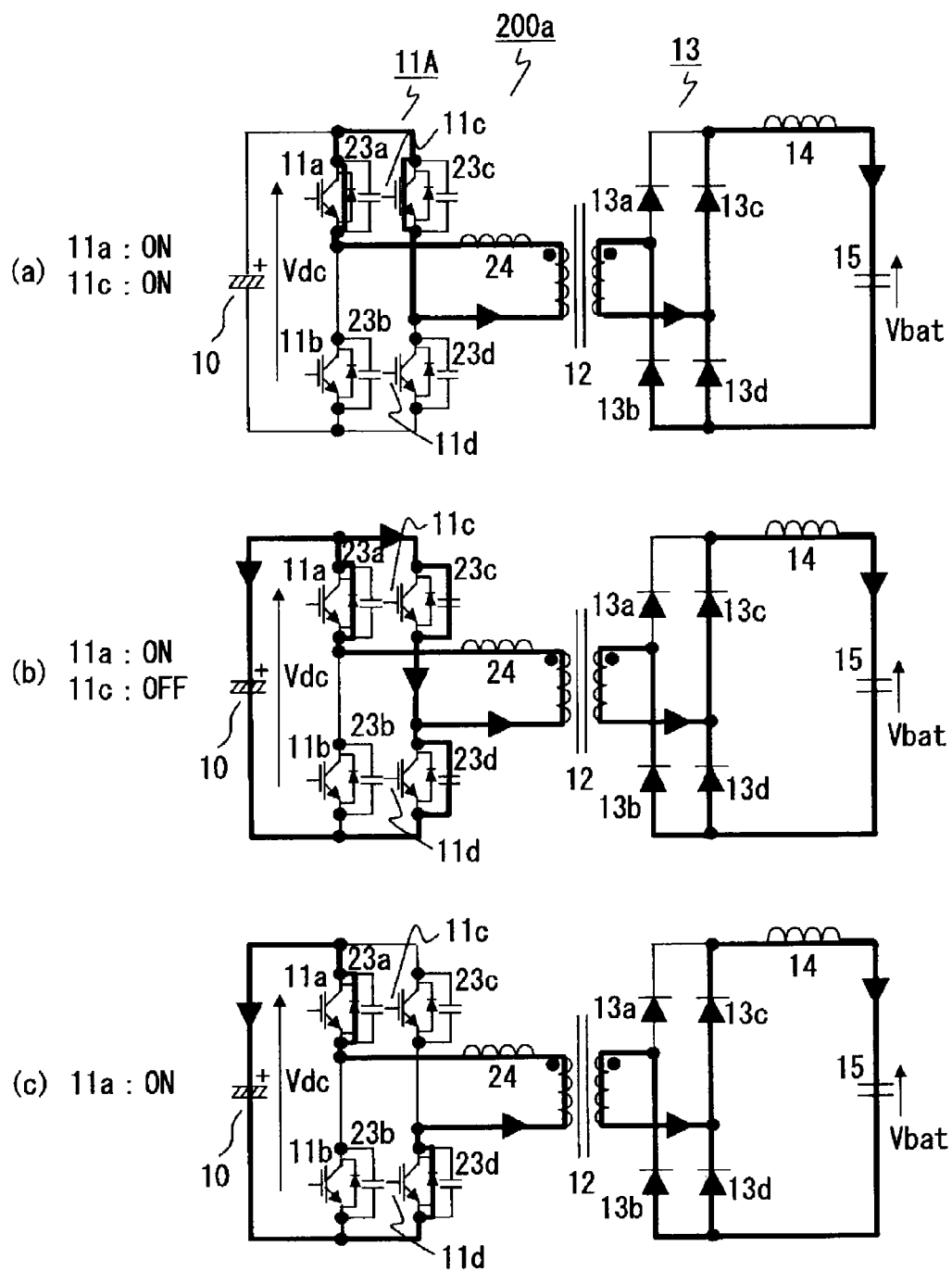


FIG. 19

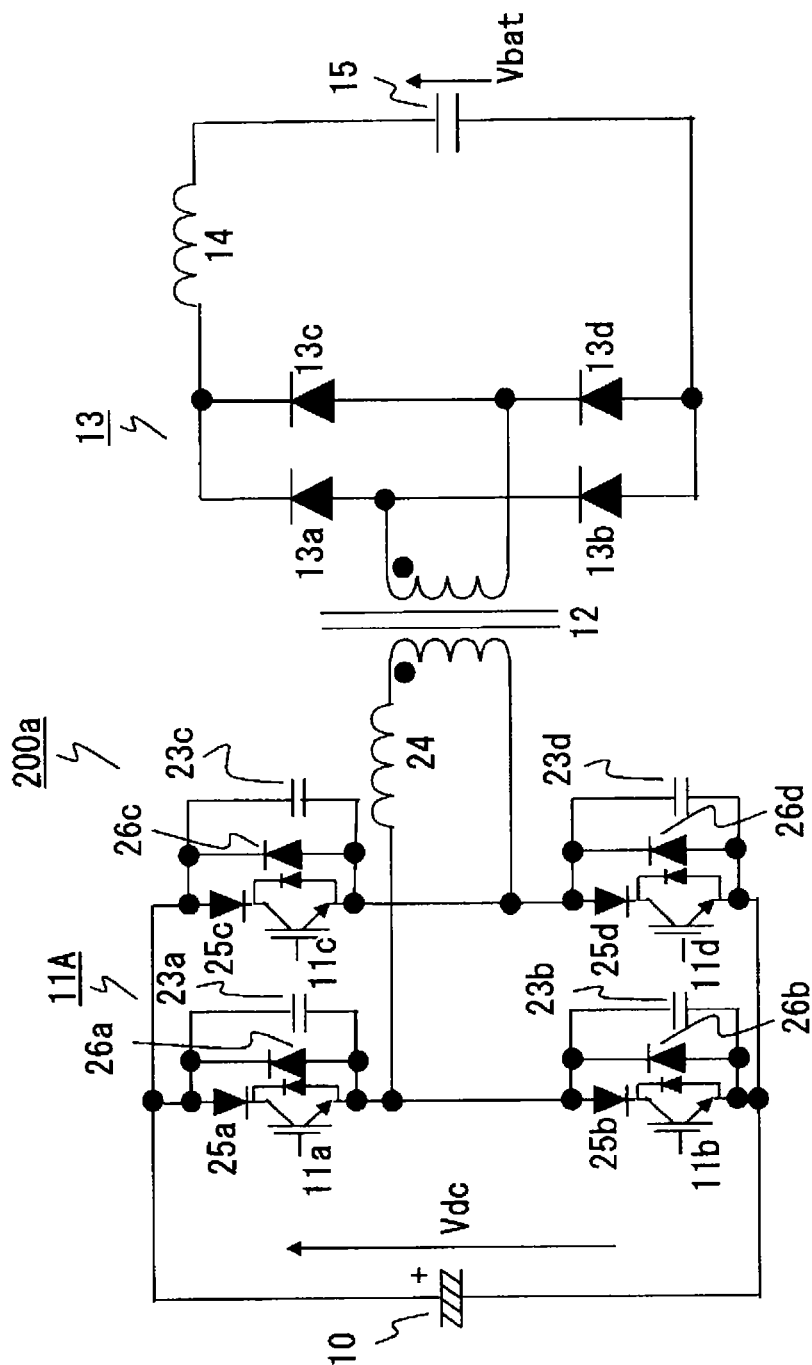


FIG. 20

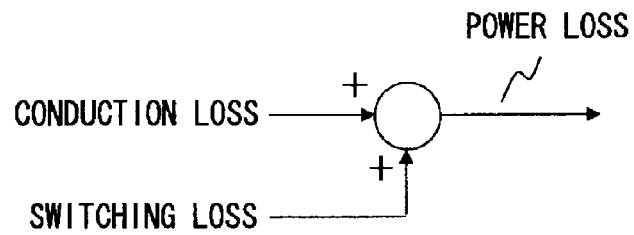


FIG. 21

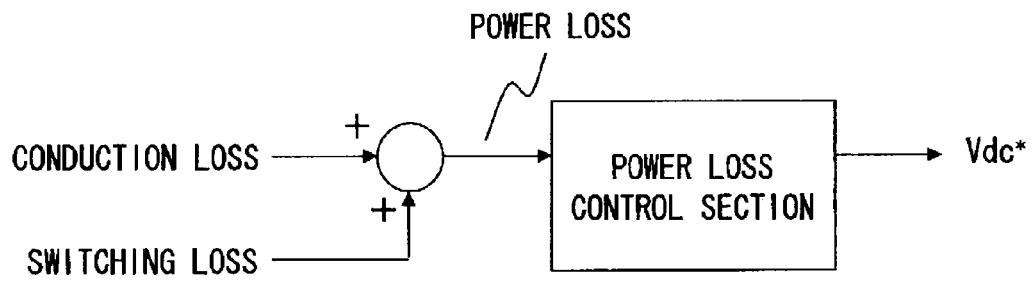


FIG. 22

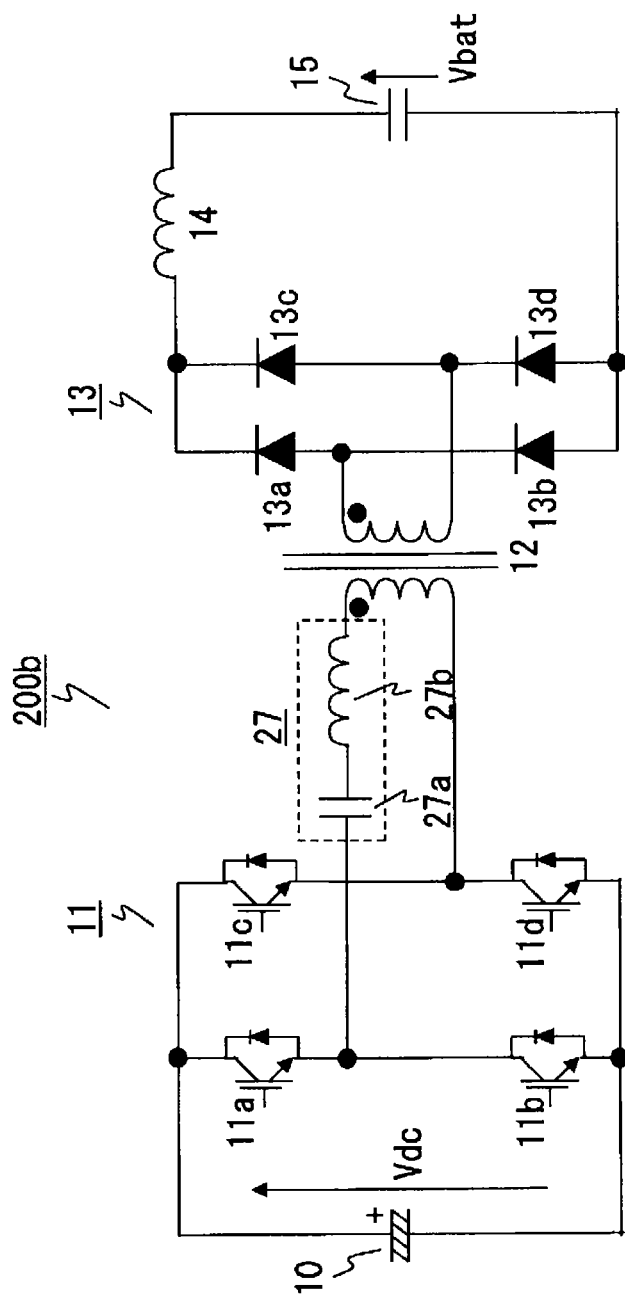


FIG. 23

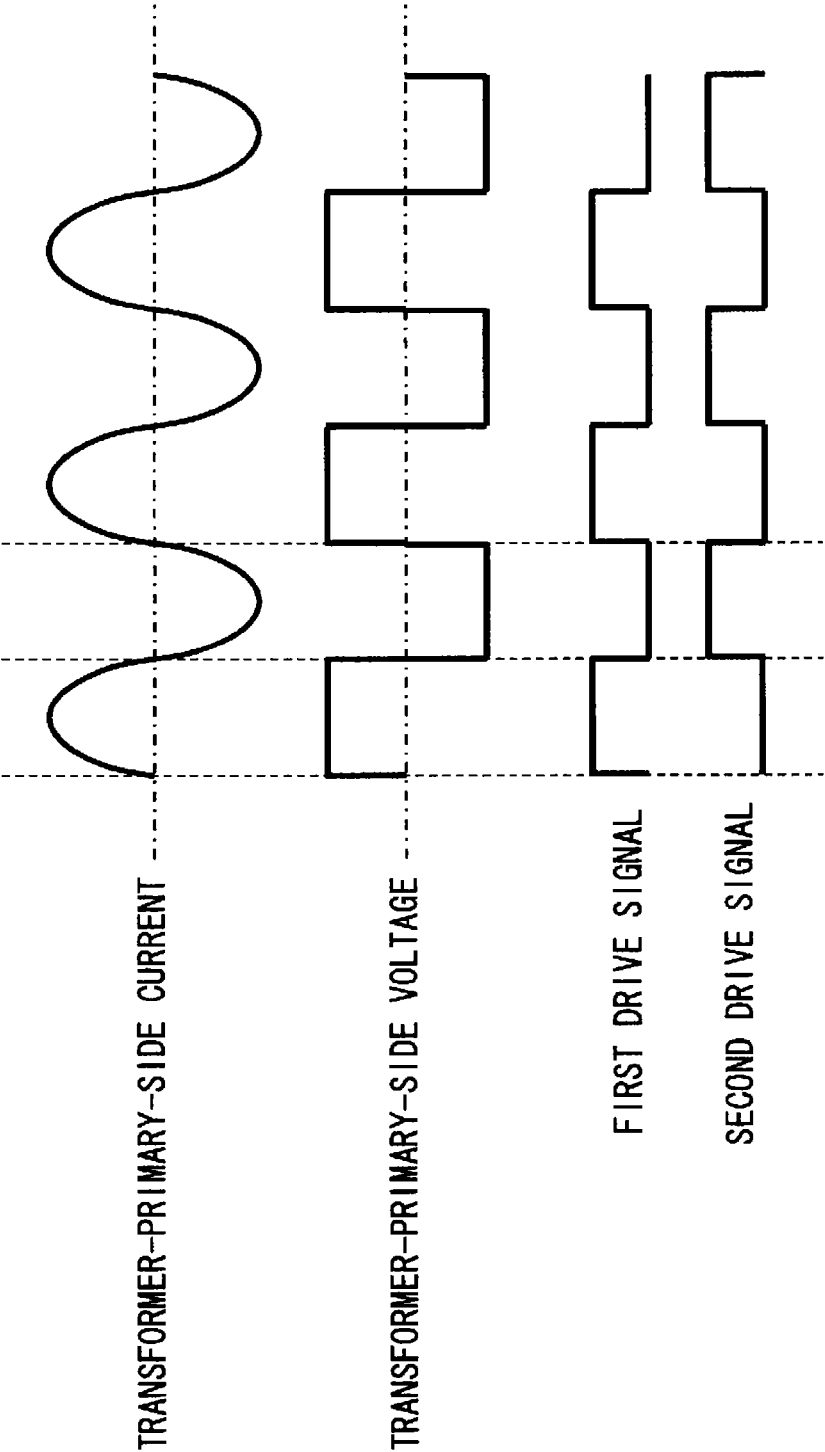


FIG. 24

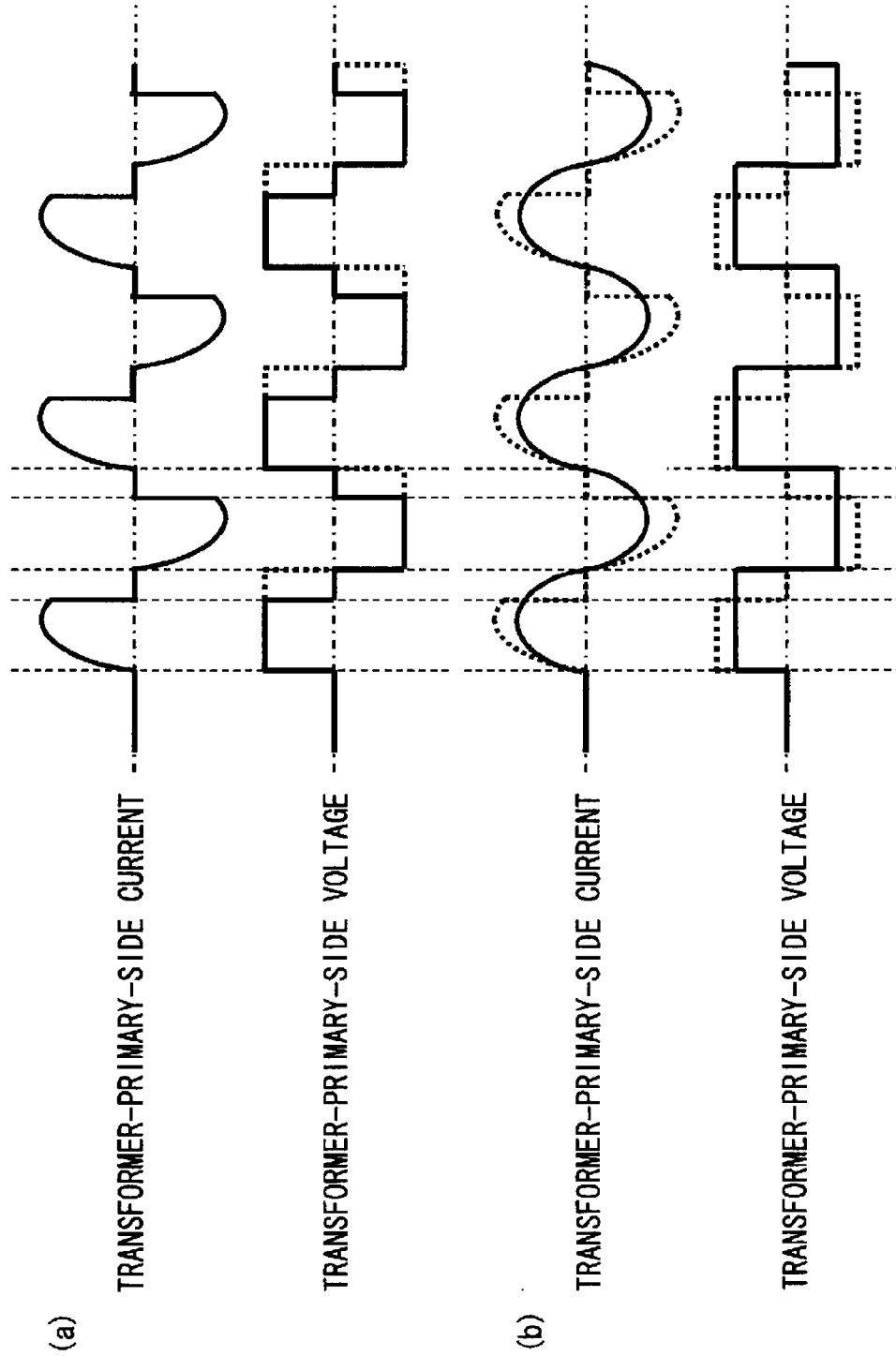
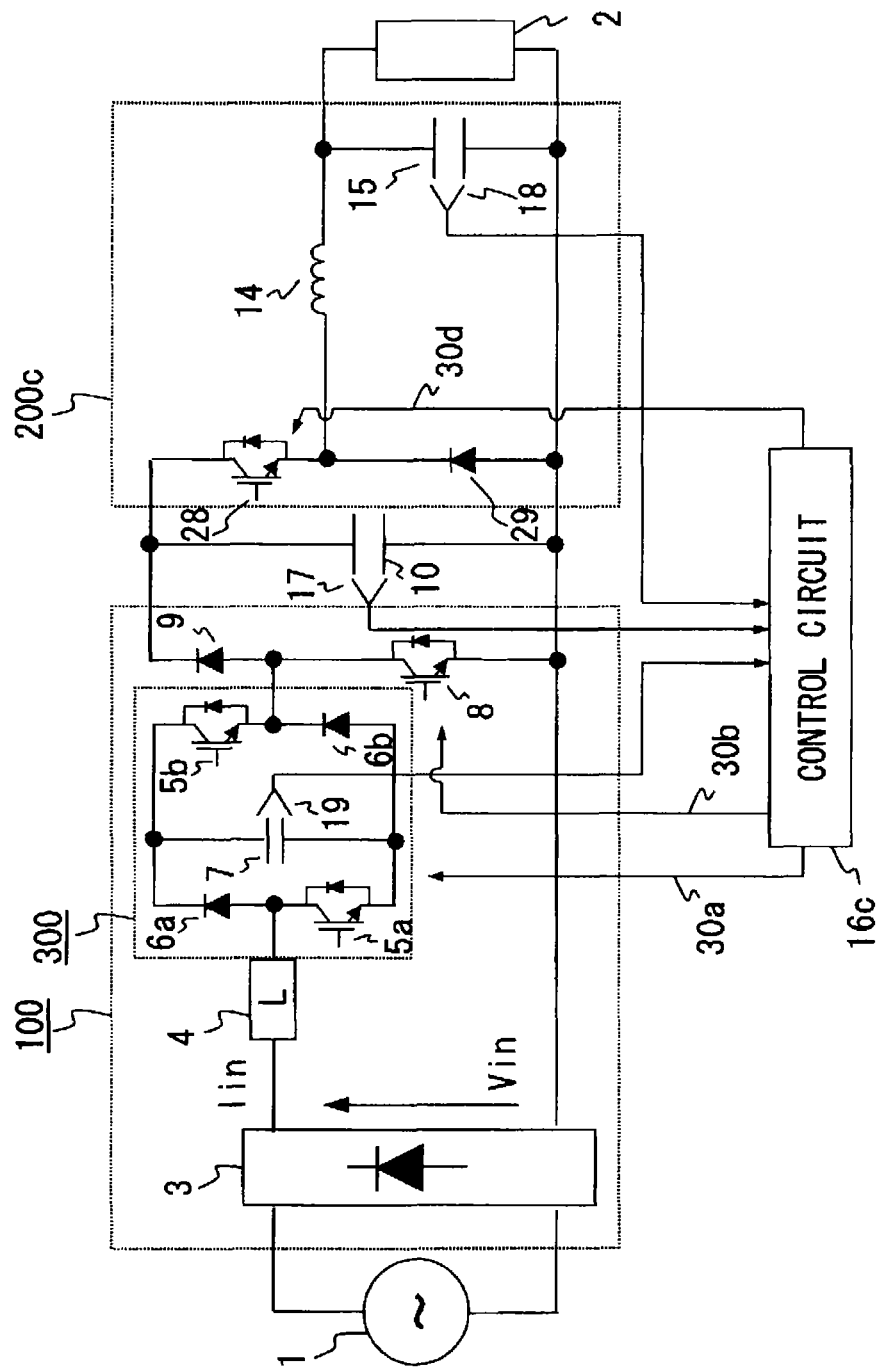




FIG. 25



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# POWER CONVERSION APPARATUS HAVING AN AC/DC CONVERTER WHICH OUTPUTS TO A DC/DC CONVERTER WHICH IS CONTROLLED BY A CONTROLLER

## TECHNICAL FIELD

The present invention relates to a power conversion apparatus comprising a circuit for improving an input power factor, the power conversion apparatus converting AC power to DC power and then obtaining a desired DC output.

## BACKGROUND ART

A conventional power conversion apparatus includes: a high-power-factor converter section which performs high-power-factor control for a commercial AC power supply and performs AC/DC conversion; and a DC/DC converter section, provided at the subsequent stage of the high-power-factor converter section, in which the primary side and the secondary side are insulated by a transformer, whereby those sections respectively charge a main battery and a subsidiary battery insulated from each other. When the main battery is preferentially charged, the duty ratio of a switching circuit on the primary side of the transformer is controlled to be constant, and the duty ratio of a switching circuit on the secondary side of the transformer is controlled to be variable. When the subsidiary battery is preferentially charged, the duty ratios of the switching circuits on the primary side and the secondary side of the transformer are controlled to be variable (for example, see Patent Document 1).

## CITATION LIST

Patent Document

Patent Document 1: Japanese Laid-Open Patent Publication No. 2008-118727

## SUMMARY OF THE INVENTION

### Problems to be Solved by the Invention

In the conventional power conversion apparatus, when the main battery or the subsidiary battery is charged, the duty ratio of the switching circuit on the secondary side of the transformer of the DC/DC converter section is controlled, or the duty ratios of the switching circuits on the primary side and the secondary side of the transformer are controlled. Thus, since control for obtaining a desired DC output is performed by duty control for the switching circuit, the variation width of the duty ratio necessarily increases, and power loss increases in the period in which the duty ratio is low. Therefore, there is a limit on reduction of power loss.

The present invention has been made to solve the above problem, and an object of the present invention is to reduce power loss and improve the power conversion efficiency, in a power conversion apparatus comprising a circuit for improving an input power factor, the power conversion apparatus converting AC power to DC power and then obtaining a desired DC output.

### Solution to the Problems

A first power conversion apparatus according to the present invention includes: an AC/DC converter section which converts an AC voltage to a DC voltage; a smoothing capacitor

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connected to the DC side of the AC/DC converter section; a DC/DC converter section, comprising a semiconductor switching device, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs the resultant power to a load; and a control apparatus which controls the AC/DC converter section such that the power factor of AC is controlled and the DC voltage of the AC/DC converter section follows a target value, and which controls the DC/DC converter section by duty control for the semiconductor switching device such that a DC input/output between the DC/DC converter section and the load follows an instruction value. The control apparatus adjusts the DC voltage target value of the AC/DC converter section in accordance with the DC input/output between the DC/DC converter section and the load.

A second power conversion apparatus according to the present invention includes: an AC/DC converter section which converts an AC voltage to a DC voltage; a smoothing capacitor connected to the DC side of the AC/DC converter section; a DC/DC converter section, comprising a semiconductor switching device, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs the resultant power to a load; and a control apparatus which controls the AC/DC converter section such that the power factor of AC is controlled and the DC voltage of the AC/DC converter section follows a target value, and which controls the DC/DC converter section by duty control for the semiconductor switching device such that a DC input/output between the DC/DC converter section and the load follows an instruction value. The control apparatus adjusts the DC voltage target value of the AC/DC converter section so as to allow the semiconductor switching device in the DC/DC converter section to perform soft switching.

### Effect of the Invention

According to the above first power conversion apparatus, the control apparatus adjusts the DC voltage target value of the AC/DC converter section in accordance with the DC input/output between the DC/DC converter section and the load. Therefore, it is possible to appropriately control the duty ratio of the semiconductor switching device in the DC/DC converter section, thereby reducing power loss of the DC/DC converter section and improving power conversion efficiency.

According to the above second power conversion apparatus, the control apparatus adjusts the DC voltage target value of the AC/DC converter section so as to allow the semiconductor switching device in the DC/DC converter section to perform soft switching. Therefore, it is possible to reduce switching loss of the semiconductor switching device in the DC/DC converter section, thereby reducing power loss of the DC/DC converter section and improving power conversion efficiency.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a configuration diagram of a power conversion apparatus according to embodiment 1 of the present invention.

FIG. 2 is a waveform diagram of each section for illustrating the operation of a high-power-factor converter section according to embodiment 1 of the present invention.

FIG. 3 is a diagram illustrating the operation of the high-power-factor converter section according to embodiment 1 of the present invention.

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FIG. 4 is a diagram illustrating the operation of the high-power-factor converter section according to embodiment 1 of the present invention.

FIG. 5 is a diagram illustrating the operation of the high-power-factor converter section according to embodiment 1 of the present invention.

FIG. 6 is a control block diagram showing the control for the high-power-factor converter section according to embodiment 1 of the present invention.

FIG. 7 is a waveform diagram of each section for illustrating the operation of a DC/DC converter section according to embodiment 1 of the present invention.

FIG. 8 is a control block diagram showing the control for the DC/DC converter section according to embodiment 1 of the present invention.

FIG. 9 shows a current waveform of a reactor for smoothing for illustrating the operation of the DC/DC converter section according to embodiment 1 of the present invention.

FIG. 10 is a control block diagram showing the control for a target voltage of a smoothing capacitor according to embodiment 1 of the present invention.

FIG. 11 is a configuration diagram of a power conversion apparatus according to another example of embodiment 1 of the present invention.

FIG. 12 is a control block diagram showing the control for a DC/DC converter section according to the other example of embodiment 1 of the present invention.

FIG. 13 is a configuration diagram of a high-power-factor converter section according to still another example of embodiment 1 of the present invention.

FIG. 14 is a configuration diagram of a power conversion apparatus according to embodiment 2 of the present invention.

FIG. 15 is a diagram illustrating zero-voltage switching operation of a DC/DC converter section according to embodiment 2 of the present invention.

FIG. 16 is a diagram illustrating zero-voltage switching operation of the DC/DC converter section according to embodiment 2 of the present invention.

FIG. 17 is a diagram illustrating zero-voltage switching operation of the DC/DC converter section according to embodiment 2 of the present invention.

FIG. 18 is a diagram illustrating zero-voltage switching operation of the DC/DC converter section according to embodiment 2 of the present invention.

FIG. 19 is a configuration diagram of a DC/DC converter section according to another example of embodiment 2 of the present invention.

FIG. 20 is a diagram illustrating power loss of a DC/DC converter section according to embodiment 3 of the present invention.

FIG. 21 is a control block diagram showing the control for a target voltage of a smoothing capacitor according to embodiment 3 of the present invention.

FIG. 22 is a configuration diagram of a DC/DC converter section according to embodiment 4 of the present invention.

FIG. 23 is a waveform diagram illustrating zero-current switching operation of the DC/DC converter section according to embodiment 4 of the present invention.

FIG. 24 is a waveform diagram illustrating the control for the DC/DC converter section according to embodiment 4 of the present invention.

FIG. 25 is a configuration diagram of a power conversion apparatus according to embodiment 5 of the present invention.

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## EMBODIMENTS OF THE INVENTION

### Embodiment 1

Hereinafter, embodiment 1 of the present invention will be described.

FIG. 1 is a diagram showing the circuit configuration of a power conversion apparatus according to embodiment 1 of the present invention. As shown in FIG. 1, a main circuit of the power conversion apparatus includes: a high-power-factor converter section **100** as an AC/DC converter, connected to an AC voltage source **1**, which controls the power factor of an input AC to be high and converts an AC voltage to a DC voltage; a smoothing capacitor **10** which smoothes a DC output of the high-power-factor converter section **100**; and a DC/DC converter section **200** which converts the voltage of the smoothing capacitor **10** to a secondary-side DC voltage insulated by a transformer **12**. In addition, a load **2** such as a battery, for example, is connected to the output of the DC/DC converter section **200**.

The high-power-factor converter section **100** includes: a diode bridge **3**, connected to the AC voltage source **1**, which processes the input AC by full-wave rectification; an inverter circuit **300** connected in series via a reactor **4**, at the subsequent stage of the diode bridge **3**; and a bridge circuit in which a short-circuit switch **8** composed of a semiconductor switching device, and a diode **9** are connected in series, at the subsequent stage of the inverter circuit **300**. The inverter circuit **300** is composed of one or more (in this case, one) single-phase inverters whose AC sides are connected in series, each single-phase inverter being composed of: semiconductor switching devices **5a** and **5b** which are self-turn-off semiconductor switching devices such as IGBTs (Insulated Gate Bipolar Transistors); diodes **6a** and **6b**; and a DC voltage source **7** composed of a capacitor. In addition, the short-circuit switch **8** one end of which is connected to the output of the diode bridge **3**, and the diode **9** whose cathode side is connected to the smoothing capacitor **10** on the output side, are connected to the output of the inverter circuit **300**.

The DC/DC converter section **200** includes: the transformer **12** that is insulated; a converter section **11**, connected to the primary side of the transformer **12**, which converts a DC voltage of the smoothing capacitor **10** to the AC voltage by a full-bridge converter composed of semiconductor switching devices **11a** to **11d**; and a diode bridge **13** which is a rectification circuit connected to the secondary side of the transformer **12**. In addition, a reactor **14** and a capacitor **15** for output smoothing, are connected to the output of the diode bridge **13**, whereby a DC voltage is outputted to the load **2**.

Further, a control circuit **16** as a control apparatus is provided outside the main circuit, and outputs drive signals **30a** and **30b** to the semiconductor switching devices **5a** and **5b** and the short-circuit switch **8** in the high-power-factor converter section **100**, and a drive signal **30c** to the semiconductor switching devices **11a** to **11d** in the DC/DC converter section **200**. In addition, a voltage  $V_{dc}$  of the smoothing capacitor **10** is monitored by a voltage sensor **17**, a voltage  $V_{out}$  of the capacitor **15** is monitored by a voltage sensor **18**, and a voltage  $V_{sub}$  of the DC voltage source **7** is monitored by a voltage sensor **19**. Then, these voltages are inputted to the control circuit **16**.

Next, operation will be described.

First, in the high-power-factor converter section **100**, an input from the AC voltage source **1** is processed by full-wave rectification by the diode bridge **3**, whereby a voltage  $V_{in}$  and a current  $I_{in}$  at the subsequent stage of the diode bridge **3** have waveforms as shown in FIG. 2.  $V_{dc}$  is the DC voltage of the

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smoothing capacitor 10, which is controlled to be a target voltage  $V_{dc}^*$  as an output voltage target value that is constant. The DC voltage  $V_{dc}$  is sensed by the voltage sensor 17.

The inverter circuit 300 controls and outputs the current  $I_{in}$  by PWM control such that the input power factor from the AC voltage source 1 is about 1, and superimposes a generated voltage on the AC side onto the voltage  $V_{in}$  at the subsequent stage of the diode bridge 3. As shown in FIGS. 3 to 5, when the semiconductor switching devices 5a and 5b are OFF, a current in the inverter circuit 300 passes through the diode 6a to charge the DC voltage source 7, and is outputted through the diode 6b. When only the semiconductor switching device 5a is ON, the current is outputted through the semiconductor switching device 5a and the diode 6b. Similarly, when only the semiconductor switching device 5b is ON, the current is outputted through the diode 6a and the semiconductor switching device 5b. When the semiconductor switching devices 5a and 5b are both ON, the current passes through the semiconductor switching device 5a to cause the DC voltage source 7 to discharge, and is outputted through the semiconductor switching device 5b. The semiconductor switching devices 5a and 5b are controlled by a combination of the above four types of control, thereby performing PWM control for the inverter circuit 300.

Here,  $\theta$  indicates the input voltage phase from the AC voltage source 1, and  $\theta_2$  ( $0 < \theta_2 < \pi/2$ ) is defined as the phase  $\theta$  where the voltage  $V_{in}$  is equal to the target voltage  $V_{dc}^*$  of the smoothing capacitor 10. The short-circuit switch 8 is ON from the phase  $\theta=0$  until a predetermined phase  $\theta_1$  ( $0 < \theta_1 < \theta_2$ ). In this case, as shown in FIG. 3, a current from the AC voltage source 1 flows through a route of the AC voltage source 1 → the diode bridge 3 → the reactor 4 → the inverter circuit 300 → the short-circuit switch 9 → the diode bridge 3 → the AC voltage source 1. Since the short-circuit switch 8 is ON, a current does not flow in the diode 9 and in the smoothing capacitor 10 at the output stage.

By PWM control, the inverter circuit 300 generates a voltage substantially equal to the opposite polarity of the voltage  $V_{in}$  by a combination of, for example, the case where the semiconductor switching devices 5a and 5b are OFF and the case where only the semiconductor switching device 5a is ON, and controls and outputs the current  $I_{in}$  such that the input power factor is about 1. During this period, the DC voltage source 7 of the inverter circuit 300 is charged with energy.

Next, at the phase  $\theta=\theta_1$ , when the short-circuit switch 8 is turned off, as shown in FIG. 4, a current from the AC voltage source 1 flows through a route of the AC voltage source 1 → the diode bridge 3 → the reactor 4 → the inverter circuit 300 → the diode 9 → the smoothing capacitor 10 → the diode bridge 3 → the AC voltage source 1.

When the phase  $\theta$  is in a range of  $\theta_1 \leq \theta \leq \theta_2$ , by PWM control, the inverter circuit 300 makes an output by a combination of, for example, the case where the semiconductor switching devices 5a and 5b are both ON and the case where only the semiconductor switching device 5a is ON. At this time, the inverter circuit 300 generates a voltage substantially equal to  $(V_{dc}^* - V_{in})$  such that the DC voltage  $V_{dc}$  of the smoothing capacitor 10 is maintained at the target voltage  $V_{dc}^*$ , and controls and outputs the current  $I_{in}$  such that the input power factor is about 1. During this period, since the polarity of a voltage generated by the inverter circuit 300 is equal to the polarity of the current  $I_{in}$ , the DC voltage source 7 of the inverter circuit 300 discharges.

Next, at the phase  $\theta=\theta_2$ , when the voltage  $V_{in}$  has become equal to the DC voltage  $V_{dc}^*$  of the smoothing capacitor 10,

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the short-circuit switch 8 continues to be OFF, but the operation of the inverter circuit 300 changes.

That is, when the phase  $\theta$  is in a range of  $\theta_2 \leq \theta \leq \pi/2$ , as shown in FIG. 5, a current from the AC voltage source 1 flows through a route of the AC voltage source 1 → the diode bridge 3 → the reactor 4 → the inverter circuit 300 → the diode 9 → the smoothing capacitor 10 → the diode bridge 3 → the AC voltage source 1. In addition, by PWM control, the inverter circuit 300 makes an output by a combination of, for example, the case where the semiconductor switching devices 5a and 5b are OFF and the case where only the semiconductor switching device 5a is ON. At this time, since the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is equal to or lower than the voltage  $V_{in}$ , the inverter circuit 300 generates a voltage being substantially equal to  $(V_{in} - V_{dc}^*)$  and having a polarity opposite to that of the voltage  $V_{in}$ , such that the DC voltage  $V_{dc}$  of the smoothing capacitor 10 is maintained at the target voltage  $V_{dc}^*$ , and controls and outputs the current  $I_{in}$  such that the input power factor is about 1. During this period, since the polarity of a voltage generated by the inverter circuit 300 is opposite to the polarity of the current  $I_{in}$ , the DC voltage source 7 of the inverter circuit 300 is charged.

As shown in FIG. 2, the operation in a phase period of  $\pi/2 \leq \theta \leq \pi$  is symmetrical to that in a phase period of  $0 \leq \theta \leq \pi/2$  described above, and the operation in a phase period of  $\pi \leq \theta \leq 2\pi$  is the same as that in a phase period of  $0 \leq \theta \leq \pi$ .

That is, when the phase  $\theta$  of the input voltage from the AC voltage source 1 is (a zero cross phase ( $\theta=0, \pi \pm \theta_1$ ), the short-circuit switch 8 is switched, and only in a range (hereinafter, referred to as a short-circuit phase range 50) between  $\pm\theta_1$  centered at the zero cross phase, the short-circuit switch 8 becomes ON, thereby bypassing the smoothing capacitor 10. At this time, the inverter circuit 300 generates a voltage substantially equal to the opposite polarity voltage of the voltage  $V_{in}$ , and controls and outputs the current  $I_{in}$  such that the input power factor is about 1, while the DC voltage source 7 is charged. Then, in the phase range other than the short-circuit phase range 50, the inverter circuit 300 maintains the DC voltage  $V_{dc}$  of the smoothing capacitor 10 at the target voltage  $V_{dc}^*$ , and controls and outputs the current  $I_{in}$  such that the input power factor is about 1. At this time, when the voltage  $V_{in}$  is equal to or lower than the target voltage  $V_{dc}^*$  of the smoothing capacitor 10, the DC voltage source 7 discharges, and when the voltage  $V_{in}$  is equal to or higher than the target voltage  $V_{dc}^*$ , the DC voltage source 7 is charged.

If  $\theta_1$  is increased, energy to charge the DC voltage source 7 increases, and thereafter, at the time of discharge, a generated voltage can be superimposed onto the voltage  $V_{in}$  in a high voltage region and energy to be discharged can be increased. Therefore, the DC voltage  $V_{dc}$  (target voltage  $V_{dc}^*$ ) of the smoothing capacitor 10 can be increased.

In a phase period of  $0 \leq \theta \leq \pi/2$ , the DC voltage source 7 of the inverter circuit 300 is charged during a period of  $0 \leq \theta \leq \theta_1$  and a period of  $\theta_2 \leq \theta \leq \pi/2$ , and discharges during a period of  $\theta_1 \leq \theta \leq \theta_2$ , as described above.

Next, the detailed operation for maintaining the DC voltage  $V_{dc}$  of the smoothing capacitor 10 at the target voltage  $V_{dc}^*$  and controlling the current  $I_{in}$  such that the input power factor is about 1 will be described below.

The high-power-factor converter section 100 is controlled in accordance with a control block as shown in FIG. 6. FIG. 6(a) is a diagram showing control for the inverter circuit 300, and FIG. 6(b) is a diagram showing control for the short-circuit switch 8 of the bridge circuit.

As shown in FIG. 6(a), in the control for the inverter circuit 300, feedback control (PI control) is performed such that a difference 51 between the DC voltage  $V_{dc}$  of the smoothing

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capacitor 10 detected by the voltage sensor 17, and the target voltage  $V_{dc}^*$  of the smoothing capacitor set in advance, approaches zero, whereby an amplitude target value 52 of the current  $I_{in}$  is determined. Then, based on the amplitude target value 52, a current instruction  $I_{in}^*$  which is a sine wave synchronized with the voltage  $V_{in}$  is generated.

Next, feedback control (PI control) is performed such that a difference 53 between the current instruction  $I_{in}^*$  and the detected current  $I_{in}$  approaches zero, whereby a voltage instruction 54 as a target value of a generated voltage of the inverter circuit 300 is outputted. At this time, the voltage instruction 54 is corrected by adding thereto a feedforward correction voltage  $\Delta V$  synchronized with a time of ON/OFF switching of the short-circuit switch B.

As described above, when the short-circuit switch 8 is switched from on to off, the capacitor 7 of the inverter circuit 300 is switched from charge to discharge, and when the short-circuit switch 8 is switched from off to on, the capacitor 7 is switched from discharge to charge. By using feedforward control at the time of the ON/OFF switching, it is possible to cancel the control delay corresponding to a response time of the feedback control, and a voltage generated between both ends of the reactor 4 for current limiting. Thus, it is possible to reduce drastic variation in a current due to the ON/OFF switching of the short-circuit switch 8.

It is noted that the feedforward correction voltage  $\Delta V$  is positive when the semiconductor switching device 8 is turned from on to off, and is negative when the semiconductor switching device 8 is turned from off to on.

Then, based on the corrected voltage instruction 55, the drive signal 30a for each of the semiconductor switching devices 5a to 5b of the inverter circuit 300 is generated by PWM control, whereby the inverter circuit 300 is operated.

On the other hand, as shown in FIG. 6(b), in the control for the short-circuit switch 8, the voltage  $V_{sub}$  of the capacitor 7 of the inverter circuit 300 detected by the voltage sensor 19 is monitored, and feedback control (PI control) is performed such that a difference 56 between the voltage  $V_{sub}$  and the target voltage  $V_{sub}^*$  of the DC voltage source 7 as a voltage instruction value set in advance approaches zero, thereby obtaining an output 57. Based on the output 57, the drive signal 30b for the short-circuit switch 8 is generated by PWM control. Thus, a phase range in which the short-circuit switch 8 is ON, that is, the short-circuit phase range 50 is also controlled.

In such control for the short-circuit switch 8, the higher the voltage value obtained by subtracting the voltage  $V_{sub}$  of the DC voltage source 7 from the target voltage  $V_{sub}^*$  is, the longer the ON-period of the short-circuit switch 8 is. Therefore, even if the voltage  $V_{sub}$  varies because of transient load variation or variation in the AC voltage source 1, it is possible to control the period for charging the DC voltage source 7, and to control the voltage  $V_{sub}$  of the DC voltage source 7 to be constant.

Therefore, without separately providing an external DC voltage source, it is possible to, in spite of transient variation in the AC voltage source 1 or a load, stabilize the voltage of the DC voltage source 7 of the inverter circuit 300 and keep the DC bus voltage of the inverter circuit 300 to be constant, thereby stably operating the high-power-factor converter section 100.

Next, operation of the DC/DC converter section 200 will be described below.

In the DC/DC converter section 200, a voltage is generated on the primary side of the transformer 12 in a period in which the semiconductor switching devices 11a and 11d are both ON and in a period in which the semiconductor switches

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devices 11b and 11c are both ON, among the semiconductor switching devices 11a to 11d of the converter section 11 on the primary side of the transformer 12, whereby power is transmitted to the secondary side. In general, the switching of the semiconductor switching devices 11a to 11d is performed by high-frequency PWM operation, such that the length of the period in which the semiconductor switching devices 11a and 11d are both ON is equal to the length of the period in which the semiconductor switches devices 11b and 11c are both ON.

FIG. 7 shows a voltage and a current generated on the secondary side of the transformer when the two semiconductor switching devices 11a and 11d (or 11b and 11c) are both ON. If  $N_1$  is the turns number of the primary winding and  $N_2$  is the turns number of the secondary winding of the transformer 12, as shown in FIG. 7, a voltage of  $V_{dc} \cdot N_2 / N_1$  is generated on the secondary winding in the period in which the two semiconductor switching devices 11a and 11d (or 11b and 11c) are both ON. As a result, a current that increases during the period in which the voltage is generated on the secondary winding and then decreases, flows in the reactor 14 for smoothing. It is noted that  $T$  is a switching cycle of the semiconductor switching devices 11a to 11d,  $\Delta t$  is ON-time in which the semiconductor switching devices 11a and 11d (or 11b and 11c) are both ON, and  $\Delta i$  is an increment in a current flowing in the reactor 14 for smoothing.

At this time, the following Expression (1) is obtained, where  $L$  is the inductance of the reactor 14 for smoothing, and  $V_{out}$  is the DC output voltage of the capacitor 15 for output.

$$\Delta i = ((V_{dc} \cdot N_2 / N_1 - V_{out}) \cdot \Delta t) / L \quad \text{Expression (1)}$$

In a period between the period in which the semiconductor switching devices 11a and 11d are both ON and the period in which the semiconductor switching devices 11b and 11c are both ON, a current on the secondary side of the transformer flows back through a route of the reactor 14 for smoothing → the capacitor 15 → the diode bridge 13 → the reactor 14 for smoothing, whereby the current decreases.

Next, control for the DC/DC converter section 200 to control the DC output voltage  $V_{out}$  to be the voltage instruction value  $V_{out}^*$  will be described below with reference to FIG. 8.

The voltage  $V_{out}$  of the capacitor 15 is sensed by the voltage sensor 18, and is outputted to the control circuit 16. In the control circuit 16, as shown in FIG. 8, the voltage  $V_{out}$  is compared with the voltage instruction value  $V_{out}^*$ , the error is amplified by an error amplifying section 19, and then the drive signal 30c (30ca and 30cb) for driving the semiconductor switching devices 11a and 11d and the semiconductor switching devices 11b and 11c of the converter section 11 is outputted by a PWM control section 20. Thus, the voltage  $V_{out}$  of the capacitor 15 is controlled so as to approach the voltage instruction value  $V_{out}^*$ .

Since in the converter section 11, the control for turning on both semiconductor switching devices 11a and 11d, and the control for turning on both semiconductor switching devices 11b and 11c, are alternately performed with the same ON-time  $\Delta t$  for each, the drive signal 30c for the semiconductor switching signals 11a to 11d is a duty instruction for determining the duty ratio ( $2\Delta t / T$ ), and each of the semiconductor switching signals 11a to 11d is duty-controlled based on the duty instruction.

Here, it will be assumed that the voltage  $V_{dc}$  of the smoothing capacitor 10, which is the output voltage of the high-power-factor converter section 100 and also the input voltage of the DC/DC converter section 200, is constant. In this case, if the output voltage  $V_{out}$  which is a DC output to the load 2 is high, the duty ratio of the semiconductor switching signals 11a to 11d is large, and if the output voltage  $V_{out}$  is low, the

duty ratio is small. When the duty ratio of the semiconductor switching devices **11a** to **11d** is decreased, the period in which the transformer **12** of the DC/DC converter section **200** transmits power from the primary side to the secondary side becomes short, and the usage rate of the transformer **12** decreases. In the periods other than the period in which the transformer **12** transmits power from the primary side to the secondary side, a current flows back on the primary side of the transformer **12**. If the flow-back period increases, power loss increases.

FIG. 9 is a diagram showing comparison between current waveforms of the reactor **14** for smoothing, depending on the difference in the duty ratio of the semiconductor switching devices **11a** to **11d**. As shown in FIG. 9, in order to obtain an average current  $i_{av}$  flowing in the reactor **14** for smoothing, in the case of using a current waveform  $ma$  in which a current mildly increases, an ON-time  $\Delta t_a$  of the semiconductor switching devices **11a** to **11d** is long so that the duty ratio is large. On the other hand, in the case of using a current waveform  $mb$  in which a current steeply increases, an ON-time  $\Delta t_b$  of the semiconductor switching devices **11a** to **11d** is short so that the duty ratio is small.

From Expression (1), a current increase gradient  $\Delta i/\Delta t$  of the reactor **14** for smoothing is a value obtained by dividing the voltage  $(V_{dc} \cdot N_2/N_1 - V_{out})$  between both ends of the reactor **14** for smoothing by the inductance  $L$  of the reactor **14** for smoothing.

Therefore, if the voltage  $V_{dc}$  is assumed to be constant, when the output voltage  $V_{out}$  increases,  $\Delta i/\Delta t$  decreases, and when the output voltage  $V_{out}$  decreases,  $\Delta i/\Delta t$  increases. That is, when the output voltage  $V_{out}$  decreases, a current in the reactor **14** for smoothing steeply increases, and the duty ratio of the semiconductor switching devices **11a** to **11d** decreases. However, even if the output voltage  $V_{out}$  is low, by decreasing the voltage  $V_{dc}$ , the increase in the voltage  $(V_{dc} \cdot N_2/N_1 - V_{out})$  between both ends of the reactor **14** for smoothing can be suppressed, so that  $\Delta i/\Delta t$  will not increase.

In the present embodiment, the voltage  $V_{dc}$  of the smoothing capacitor **10** can be controlled in accordance with the output voltage  $V_{out}$ . That is, if the output voltage  $V_{out}$  is low, by decreasing the voltage  $V_{dc}$ , it is possible to always mildly increase the current in the reactor **14** for smoothing and to maintain the duty ratio of the semiconductor switching devices **11a** to **11d** to be large. For example, if the voltage  $(V_{dc} \cdot N_2/N_1 - V_{out})$  between both ends of the reactor **14** for smoothing is controlled to be constant at an appropriate value,  $\Delta i/\Delta t$  is also constant, and the current waveform of the reactor **14** for smoothing is also constant. As a result, for example, the current waveform  $ma$  having a large duty ratio as shown in FIG. 9 can be always obtained.

Next, a variable control method for the voltage  $V_{dc}$  of the smoothing capacitor **10** will be described.

As shown in FIG. 8, the control circuit **16** generates the drive signal **30c** as a duty instruction for the converter section **11** on the primary side of the transformer of the DC/DC converter section **200** such that the output voltage  $V_{out}$  follows the voltage instruction value  $V_{out}^*$ . Then, as shown in FIG. 10, the control circuit **16** performs feedback control such that the difference between a predetermined duty set value and the generated duty instruction approaches zero, thereby generating the target voltage  $V_{dc}^*$  of the smoothing capacitor **10**. Then, as shown in FIG. 6(a), the control circuit **16** generates the current instruction  $i_{in}^*$  such that the voltage  $V_{dc}$  of the smoothing capacitor **10** follows the target voltage  $V_{dc}^*$ , thereby controlling the inverter circuit **300** of the high-power-factor converter section **100**.

For example, in the case where the generated duty instruction is lower than the duty set value, a correction value by feedback control shown in FIG. 10 is negative, and therefore, the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** decreases. That is, the target voltage  $V_{dc}^*$  in the control for the high-power-factor converter section **100** shown in FIG. 6(a) decreases. Then, when the voltage  $V_{dc}$ , which is the output voltage of the high-power-factor converter section **100** and also the input voltage of the DC/DC converter section **200**, has decreased, the output voltage  $V_{out}$  of the DC/DC converter section **200** is to decrease. Then, as shown in FIG. 8, the duty instruction for the converter section **11** of the DC/DC converter section **200** increases. Thus, the duty instruction approaches the duty set value.

On the other hand, in the case where the generated duty instruction is higher than the duty set value, a correction value by feedback control shown in FIG. 10 is positive, and therefore, the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** increases. Then, when the target voltage  $V_{dc}^*$  in the control for the high-power-factor converter section **100** shown in FIG. 6(a) has increased and the voltage  $V_{dc}$  has increased, the output voltage  $V_{out}$  of the DC/DC converter section **200** is to increase. Then, as shown in FIG. 8, the duty instruction for the converter section **11** of the DC/DC converter section **200** decreases. Thus, the duty instruction approaches the duty set value.

If the voltage instruction value  $V_{out}^*$  increases, the duty instruction increases as shown in FIG. 8, but if the duty instruction becomes higher than the duty set value, the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** increases to suppress the duty instruction. On the other hand, if the voltage instruction value  $V_{out}^*$  decreases, the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** decreases to suppress the decrease in the duty instruction. Since the output voltage  $V_{out}$  is controlled by the voltage instruction value  $V_{out}^*$ , as described above, it is possible to realize control that adjusts the voltage  $V_{dc}$  to be low when the output voltage  $V_{out}$  is low, and to be high when the output voltage  $V_{out}$  is high.

As described above, in accordance with the output voltage  $V_{out}$  of the DC/DC converter section **200** which is a DC output to the load **2**, the control circuit **16** adjusts the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** such that the duty ratio of the semiconductor switching devices **11a** to **11d** of the DC/DC converter section **200** approaches the duty set value, thereby controlling the high-power-factor converter section **100** and the DC/DC converter section **200**.

As described above, if an optimum duty ratio that increases the period in which the transformer **12** transmits power from the primary side to the secondary side is used as the duty set value, the DC/DC converter section **200** can be operated in an optimum condition, and the flow-back time of a current on the primary side of the transformer **12**, and the regeneration time of power can be reduced. Therefore, it becomes possible to reduce power loss and improve power conversion efficiency, thereby reducing the size of the apparatus.

In addition, since the current increase gradient of the reactor **14** for smoothing can be controlled to be substantially constant regardless of the magnitude of the output voltage  $V_{out}$ , it becomes possible to reduce the size of the reactor **14** for smoothing.

In the above embodiment 1, the DC output voltage  $V_{out}$  is controlled as a DC output to the load **2**, but a DC output current  $i_{out}$  may be controlled. In this case, as shown in FIG. 11, a current sensor **22** is provided between the capacitor **15** for output smoothing and the load **2**, thereby detecting the output current  $i_{out}$  as a DC output, and the detected value is inputted to a control circuit **16a** as a control apparatus. At this

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time, as shown in FIG. 12, the control circuit 16a compares the output current  $I_{out}$  with the output current instruction value  $I_{out}^*$ , amplifies the error by the error amplifying section 19, and outputs the drive signal 30c (30ca and 30cb) for driving the semiconductor switching devices 11a and 11d and the semiconductor switching devices 11b and 11c of the converter section 11 by the PWM control section 20. Thus, the output current  $I_{out}$  to the load 2 is controlled so as to approach the current instruction value  $I_{out}^*$ .

The other operations of the control circuit 16a are the same as those of the control circuit 16 of the above embodiment 1. That is, in accordance with the output current  $I_{out}$  of the DC/DC converter section 200 as a DC output to the load 2, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is adjusted such that the duty ratio of the semiconductor switching devices 11a to 11d of the DC/DC converter section 200 approaches the duty set value, whereby the high-power-factor converter section 100 and the DC/DC converter section 200 are controlled. Thus, the same effect as in the above embodiment 1 can be provided.

The above embodiment has described that if the voltage instruction value  $V_{out}^*$  increases, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 increases, and if the voltage instruction value  $V_{out}^*$  decreases, the target voltage  $V_{dc}^*$  decreases. Here, the original target voltage  $V_{dc}^*$  of the smoothing capacitor 10 when the voltage instruction value  $V_{out}^*$  is to be changed may be set so as to optimize the duty ratio of the semiconductor switching devices 11a to 11d of the DC/DC converter section 200. Thus, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is first determined based on the voltage instruction value  $V_{out}^*$  such that the duty ratio of the semiconductor switching devices 11a to 11d is optimized, that is, becomes the duty set value.

Also in this case, if the voltage instruction value  $V_{out}^*$  increases, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 increases, and if the voltage instruction value  $V_{out}^*$  decreases, the target voltage  $V_{dc}^*$  decreases. Thereafter, in accordance with the output voltage  $V_{out}$  of the DC/DC converter section 200, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is adjusted such that the duty ratio of the semiconductor switching devices 11a to 11d of the DC/DC converter section 200 approaches the duty set value, whereby the same control as in the above embodiment 1 is performed. Thus, the same effect as in the above embodiment 1 can be provided.

In this case, even if the control for adjusting the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 such that the duty ratio of the semiconductor switching devices 11a to 11d approaches the duty set value in accordance with the output voltage  $V_{out}$  is omitted, since the target voltage  $V_{dc}^*$  is determined in accordance with the voltage instruction value  $V_{out}^*$  so as to optimize the duty ratio of the semiconductor switching devices 11a to 11d, the effect of reducing power loss and reducing the size of the apparatus can be provided.

The semiconductor switching devices 5a and 5b and 11a to 11d which are self-turn-off semiconductor switching devices may be GCTs, GTOs, transistors, MOSFETs, or the like, instead of IGBTs. In the single-phase inverter of the inverter circuit 300, self-turn-off semiconductor switching devices may be used instead of the diodes 6a and 6b. Further, the inverter circuit 300 may have another circuit configuration.

The configuration of the AC/DC converter section is not limited to the high-power-factor converter section 100. A high-power-factor converter section 100a having a configuration as shown in FIG. 13 may be used. In this case, an inverter circuit 300a composed of a single-phase inverter having the semiconductor switching devices 5a to 5d is con-

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nected to the AC voltage source 1 via the reactor 4, and a bridge circuit in which short-circuit switches 8a and 8b composed of semiconductor switching devices, and diodes 9a and 9b are connected in series, respectively, is provided at the subsequent stage of the inverter circuit 300a. It is noted that any high-power-factor converter that converts an AC voltage to a DC voltage may be applied to the high-power-factor converter section.

Also, the configuration of the DC/DC converter section 200 is not limited to the above-described one. The converter section 11 may have another circuit configuration such as a half-bridge converter, instead of the full-bridge converter circuit. In addition, also on the secondary side of the transformer 12, a rectification circuit other than the diode bridge 13 may be used.

## Embodiment 2

Next, embodiment 2 of the present invention will be described.

FIG. 14 is a diagram showing the circuit configuration of a power conversion apparatus according to embodiment 2 of the present invention. As shown in FIG. 14, a DC/DC converter section 200a includes, on the primary side of the transformer 12 that is insulated, a converter section 11A which is a full-bridge converter having the semiconductor switching devices 11a to 11d and which converts a DC voltage of the smoothing capacitor 10 to an AC voltage. The converter section 11A is a zero-voltage switching circuit that allows the voltage between both ends of each of the semiconductor switching devices 11a to 11d at the time of switching to be substantially zero. Capacitors 23a to 23d are connected in parallel to the semiconductor switching devices 11a to 11d, respectively. In addition, a reactor 24 is connected to an AC output line between the semiconductor switching devices 11a to 11d and the transformer 12.

A control circuit 16b as a control apparatus outputs the drive signals 30a and 30b for the semiconductor switching devices 5a and 5b and the short-circuit switch 8 in the high-power-factor converter section 100, and the drive signal 30c as a duty instruction for the semiconductor switching devices 11a to 11d in the DC/DC converter section 200. Here, the drive signal 30c for the semiconductor switching devices 11a to 11d is generated and outputted so as to allow the semiconductor switching devices 11a to 11d to perform zero-voltage switching. The other configurations are the same as those shown in FIG. 11 in the above embodiment 1.

First, the zero-voltage switching operation will be described. FIGS. 15 to 18 are diagrams illustrating the operation of the DC/DC converter section 200a, and show the current routes in the DC/DC converter section 200a at each phase of the variation in the switching states of the semiconductor switching devices 11a to 11d. It is noted that the diode bridge 13 is shown as diodes 13a to 13d in the drawings.

As shown in FIG. 15(a), when the semiconductor switching devices 11a and 11d are ON, a current flows on the primary side of the transformer 12 through a route of the smoothing capacitor 10→the semiconductor switching device 11a→the reactor 24→the transformer 12→the semiconductor switching device 11d→the smoothing capacitor 10. At this time, a current flows on the secondary side of the transformer 12 through a route of the transformer 12→the diode 13a→the reactor 14→the capacitor 15→the diode 13d→the transformer 12, whereby power is transmitted from the primary side to the secondary side of the transformer 12.

Next, as shown in FIG. 15(b), when the semiconductor switching device 11a has been turned off, a current flows on

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the primary side of the transformer through a route of the reactor 24→the transformer 12→the semiconductor switching device 11d→the smoothing capacitor 10→the capacitor 23a→the reactor 24, and a route of the reactor 24→the transformer 12→the semiconductor switching device 11d→the capacitor 23b→the reactor 24. At this time, the increase in the voltage between both ends of the semiconductor switching device 11a is delayed by effect of the capacitor 23a, whereby a current is interrupted before the voltage increases. Such switching is generally referred to as zero-voltage switching, which reduces switching loss to substantially zero.

In addition, since the sum of the voltages of the capacitor 23a and the capacitor 23b is equal to the voltage of the smoothing capacitor 10, the increase in the voltage between both ends of the capacitor 23a is substantially equal to the decrease in the voltage between both ends of the capacitor 23b. At this time, a current flows on the secondary side of the transformer 12, by the energy of the reactor 14, through a route of the reactor 14→the capacitor 15→the diode 13b→the diode 13a→the reactor 14, or a route of the reactor 14→the capacitor 15→the diode 13d→the transformer 12→the diode 13a→the reactor 14. The state shown in FIG. 15(b) continues until the voltage of the capacitor 23a becomes substantially equal to the voltage of the smoothing capacitor 10 and the voltage of the capacitor 23b becomes substantially zero.

Next, when the voltage of the capacitor 23a has become substantially equal to the voltage of the capacitor 10 and the voltage of the capacitor 23b has become substantially zero, as shown in FIG. 15(c), a current flows on the primary side of the transformer 12 through a route of the reactor 24→the transformer 12→the semiconductor switching device 11d→the antiparallel diode of the semiconductor switching device 11b→the reactor 24.

Next, as shown in FIG. 16(a), when the semiconductor switching device 11b has been turned on so that the semiconductor switching devices 11b and 11d have become ON, if the semiconductor switching devices 11a to 11d are devices such as IGBTs that do not allow a current to flow in an opposite direction, the current flowing route does not change from the case of FIG. 15(c). At this time, the voltage between both ends of the semiconductor switching device 11b (the voltage of the capacitor 23b) is substantially zero, that is, zero-voltage switching is performed, whereby switching loss of the semiconductor switching device 11b is substantially zero.

Next, as shown in FIG. 16(b), when the semiconductor switching device 11d has been turned off, a current flows on the primary side of the transformer 12 through a route of the reactor 24→the transformer 12→the capacitor 23d the antiparallel diode of the semiconductor switching device 11b→the reactor 24, and a route of the reactor 24→the transformer 12→the capacitor 23c→the smoothing capacitor 10→the antiparallel diode of the semiconductor switching device 11b→the reactor 24. At this time, in the semiconductor switching device 11d, a current is interrupted before the voltage between both ends thereof increases, by effect of the capacitor 23d, whereby zero-voltage switching is performed. Then, a current flows in the state shown in FIG. 16(b) until the voltage of the capacitor 23c decreases to substantially zero and the voltage of the capacitor 23d becomes substantially equal to the voltage of the smoothing capacitor 10.

Next, when the voltage of the capacitor 23c has decreased to substantially zero and the voltage of the capacitor 23d has become substantially equal to the voltage of the smoothing capacitor 10, as shown in FIG. 16(c), a current flows on the primary side of the transformer 12 through a route of the reactor 24→the transformer 12→the antiparallel diode of the

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semiconductor switching device 11c→the smoothing capacitor 10→the antiparallel diode of the semiconductor switching device 11b→the reactor 24.

Next, as shown in FIG. 17(a), when the semiconductor switching device 11c has been turned on so that the semiconductor switching devices 11b and 11c have become ON, a voltage in the opposite direction is applied to the transformer 12 and the reactor 24, and a current flows on the primary side of the transformer 12 through a route of the smoothing capacitor 10→the semiconductor switching device 11c→the transformer 12→the reactor 24→the semiconductor switching device 11b→the smoothing capacitor 10. At this time, a current flows on the secondary side of the transformer 12 through a route of the transformer 12→the diode 13c→the reactor 14→the capacitor 15→the diode 13b→the the transformer 12, whereby power is transmitted from the primary side to the secondary side of the transformer 12. At this time, the semiconductor switching device 11c is turned on with the voltage between both ends thereof being substantially zero, that is, zero-voltage switching is performed. Therefore, switching loss hardly occurs.

Next, as shown in FIG. 17(b), when the semiconductor switching device 11b has been turned off, a current flows on the primary side of the transformer through a route of the reactor 24→the capacitor 23b→the smoothing capacitor 10→the semiconductor switching device 11c→the transformer 12→the reactor 24, and a route of the reactor 24→the capacitor 23a→the semiconductor switching device 11c→the transformer 12→the reactor 24. At this time, in the semiconductor switching device 11b, a current is interrupted before the voltage between both ends thereof increases, by effect of the capacitor 23b, whereby zero-voltage switching is performed.

In addition, at this time, a current flows on the secondary side of the transformer 12, by the energy of the reactor 14, through a route of the reactor 14→the capacitor 15→the diode 13d→the diode 13c→the reactor 14, or a route of the reactor 14→the capacitor 15→the diode 13b→the transformer 12→the diode 13c→the reactor 14. Then, a current flows in the state shown in FIG. 17(b) until the voltage of the capacitor 23a decreases to substantially zero and the voltage of the capacitor 23b becomes substantially equal to the voltage of the smoothing capacitor 10.

Next, when the voltage of the capacitor 23a has decreased to substantially zero and the voltage of the capacitor 23b has become substantially equal to the voltage of the smoothing capacitor 10, as shown in FIG. 17(c), a current flows on the primary side of the transformer 12 through a route of the reactor 24→the antiparallel diode of the semiconductor switching device 11a→the semiconductor switching device 11c→the transformer 12→the reactor 24.

Next, as shown in FIG. 18(a), when the semiconductor switching device 11a has been turned on so that the semiconductor switching devices 11a and 11c have become ON, the current flowing route does not change from the case of FIG. 17(c). At this time, the voltage between both ends of the semiconductor switching device 11a (the voltage of the capacitor 23a) is substantially zero, that is, zero-voltage switching is performed, whereby switching loss of the semiconductor switching device 11a is substantially zero.

Next, as shown in FIG. 18(b), when the semiconductor switching device 11c has been turned off, a current flows on the primary side of the transformer 12 through a route of the reactor 24→the antiparallel diode of the semiconductor switching device 11a→the capacitor 23c→the transformer 12→the reactor 24, and a route of the reactor 24→the antiparallel diode of the semiconductor switching device



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11a→the smoothing capacitor 10→the capacitor 23d→the transformer 12→the reactor 24. At this time, in the semiconductor switching device 11c, a current is interrupted before the voltage between both ends thereof increases, by effect of the capacitor 23c, whereby zero-voltage switching is performed. Then, a current flows in the state shown in FIG. 18(b) until the voltage of the capacitor 23d decreases to substantially zero and the voltage of the capacitor 23c becomes substantially equal to the voltage of the smoothing capacitor 10.

Next, when the voltage of the capacitor 23d has decreased to substantially zero and the voltage of the capacitor 23c has become substantially equal to the voltage of the smoothing capacitor 10, as shown in FIG. 18(c), a current flows on the primary side of the transformer 12 through a route of the reactor 24→the antiparallel diode of the semiconductor switching device 11a→the smoothing capacitor 10→the antiparallel diode of the semiconductor switching device 11d→the transformer 12→the reactor 24. Then, the semiconductor switching device 11d is turned on, and the state returns to that of FIG. 15(a).

A condition for the above-described zero-voltage switching of the semiconductor switching devices 11a to 11d will be described below.

In zero-voltage switching of each of the semiconductor switching devices 11a to 11d, the capacitors 23a to 23d connected in parallel to the semiconductor switching devices 11a to 11d respectively exert effects. The condition for realizing the zero-voltage switching of the semiconductor switching devices 11a to 11d is that the voltages of the capacitors 23a to 23d increase to the voltage of the smoothing capacitor 10 or decrease to be close to zero during the dead time of switching.

Since the voltages of the capacitors 23a to 23d vary in accordance with the current in the reactor 24, if the output power of the DC/DC converter section 200a is small, that is, if the current in the reactor 24 decreases, there is a possibility that the above realization condition is not satisfied and the zero-voltage switching of the semiconductor switching devices 11a to 11d cannot be performed.

Therefore, in order that each of the semiconductor switching devices 11a to 11d can satisfy the above realization condition to perform zero-voltage switching, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is changed in accordance with the current in the reactor 24. That is, if the current in the reactor 24 is small so that the zero-voltage switching cannot be performed, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is decreased. In the case where the output power of the DC/DC converter section 200a is the same value, if the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is decreased to decrease the voltage  $V_{dc}$  so that the output voltage  $V_{out}$  has decreased, the current in the reactor 24 increases by the amount corresponding to said decrease. As a result, since the voltage variations in the capacitors 23a to 23d during the dead time of the switching of the semiconductor switching devices 11a to 11d become large, zero-voltage switching becomes easy to be realized. In addition, also by decrease in the voltage of the smoothing capacitor 10, zero-voltage switching becomes easy to be realized.

Also in the present embodiment, as in the above embodiment 1, the control circuit 16b controls the high-power-factor converter section 100 as shown in FIGS. 6(a) and 6(b). In addition, as shown in FIG. 8 or 12, the control circuit 16b performs duty control for the semiconductor switching devices 11a to 11d such that the output voltage  $V_{out}$  or the output current  $I_{out}$  as a DC output follows an instruction value, thereby controlling the DC/DC converter section 200a. At this time, the semiconductor switching devices 11a to 11d

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are caused to perform switching operations as shown in FIGS. 15 to 18. Then, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is adjusted, whereby zero-voltage switching of the semiconductor switching devices 11a to 11d is enabled.

Thus, it becomes possible to significantly decrease the switching loss of the semiconductor switching devices 11a to 11d in the DC/DC converter section 200a, thereby reducing the power loss of the power conversion apparatus and improving the power conversion efficiency.

It is noted that a leakage inductance of the transformer 12 may be used to serve as the reactor 24 connected to the AC output line of the converter section 11 on the primary side of the transformer 12.

In the case where the semiconductor switching devices 11a to 11d are composed of MOSFETs, synchronized rectification operation which does not allow a current to pass through the antiparallel diode may be performed.

The DC/DC converter section 200a may have a circuit configuration as shown in FIG. 19. As shown in FIG. 19, in the converter section 11A of the DC/DC converter section 200a, diodes 25a to 25d for preventing reverse conduction are connected in series to the semiconductor switching devices 11a to 11d, respectively, and antiparallel diodes 26a to 26d are connected in parallel to the respective series circuits composed of the semiconductor switching devices 11a to 11d and the diodes 25a to 25d for preventing reverse conduction. In this case, only a forward current is applied to the semiconductor switching devices 11a to 11d, and a reverse current is applied to the antiparallel diodes 26a to 26d. The other configurations are the same as those shown in FIG. 14 in the above embodiment 2.

In the power conversion apparatus having the circuit configuration described in the present embodiment, the control described in the above embodiment 1 may be performed, and at this time, the semiconductor switching devices 11a to 11d may be caused to perform switching operations as shown in FIGS. 15 to 18, whereby zero-voltage switching of the semiconductor switching devices 11a to 11d may be performed. In this case, in accordance with the DC output of the DC/DC converter section 200a, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is adjusted such that the duty ratio of the semiconductor switching devices 11a to 11d approaches the duty set value. As described above, since the duty set value is set at a relatively large value of duty ratio, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is suppressed to be relatively low. Therefore, the current in the reactor 24 can be maintained at a relatively high value, whereby zero-voltage switching of the semiconductor switching devices 11a to 11d can be realized. In this case, the same effect as in the above embodiment 1 can be provided, and further, it becomes possible to significantly decrease the switching loss of the semiconductor switching devices 11a to 11d, thereby further improving the power conversion efficiency.

#### Embodiment 3

In the above embodiment 2, zero-voltage switching of the semiconductor switching devices 11a to 11d is performed, thereby reducing switching loss to substantially zero. In embodiment 3, instead of using a voltage that is absolutely zero, a minute voltage is permitted, to perform switching of the semiconductor switching devices 11a to 11d. It is noted that the circuit configuration of the power conversion apparatus is the same as that of the above embodiment 2 (see FIGS. 14 and 19).

FIG. 20 is a diagram illustrating power loss in the semiconductor switching devices 11a to 11d of the DC/DC con-

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verter section **200a** according to embodiment 3. As shown in FIG. **20**, the power loss that is the sum of switching loss at the time of switching and conduction loss at the time of conduction occurs in the semiconductor switching devices **11a** to **11d**.

When the output power of the DC/DC converter section **200a** is small, a current flowing in the reactor **24** becomes small. Therefore, for example, after the semiconductor switching device **11a** has been turned from on to off, if the voltage of the capacitor **23b** does not completely decrease to zero until the semiconductor switching device **11b** is turned on after switching dead time, energy corresponding to the remaining voltage of the capacitor **23b** is switching loss of the semiconductor switching device **11b**.

As described above, if the DC voltage  $V_{dc}$  of the smoothing capacitor **10** is decreased to increase a current flowing in the reactor **24**, it is possible to realize the operation that allows the voltage of the capacitor **23b** to become zero during the switching dead time between the semiconductor switching device **11a** and the semiconductor switching device **11b**. At this time, zero-voltage switching is performed in the semiconductor switching devices **11a** to **11d**, and therefore, switching loss is substantially zero. However, since a current flowing in the reactor **24**, that is, a current flowing in the semiconductor switching devices **11a** to **11d** increases, conduction loss of the semiconductor switching devices **11a** to **11d** increases.

Accordingly, in embodiment 3, the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** is adjusted so as to decrease power loss which is the sum of the conduction loss and the switching loss of the semiconductor switching devices **11a** to **11d**. For this adjustment, the voltage  $V_{dc}$  of the smoothing capacitor **10** that minimizes the power loss of the semiconductor switching devices **11a** to **11d** may be obtained in advance, and the voltage value may be used as the target voltage  $V_{dc}^*$ .

Thus, although the switching of the semiconductor switching devices **11a** to **11d** is not perfect zero-voltage switching, conduction loss of the semiconductor switching devices **11a** to **11d** can be reduced, and power loss which is the sum of conduction loss and switching loss can be further reduced. Therefore, it is possible to realize a power conversion apparatus having decreased loss.

It is noted that the target voltage  $V_{dc}^*$  may be set such that power loss of the semiconductor switching devices **11a** to **11d** is equal to or smaller than a predetermined value set in advance. For example, if a value corresponding to conduction loss at the time of zero-voltage switching is used as the predetermined value set in advance, the power loss which is the sum of the conduction loss and the switching loss can be reduced.

As shown in FIG. **21**, a power loss control section may be provided in the control circuit **16b**. In this case, in the control circuit **16b**, the power loss which is the sum of the conduction loss and the switching loss of the semiconductor switching devices **11a** to **11d** is calculated, and the power loss control section adjusts the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** so as to decrease the power loss.

#### Embodiment 4

Next, embodiment 4 of the present invention will be described.

FIG. **22** is a diagram showing the circuit configuration of a DC/DC converter section **200b** of a power conversion apparatus according to embodiment 4 of the present invention. As shown in FIG. **22**, the DC/DC converter section **200b**

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includes, on the primary side of the transformer **12** that is insulated, the converter section **11** which is a full-bridge converter having the semiconductor switching devices **11a** to **11d** and which converts a DC voltage of the smoothing capacitor **10** to an AC voltage. The converter section **11** is a zero-current switching circuit that allows a current flowing in each of the semiconductor switching devices **11a** to **11d** at the time of switching to be substantially zero. A series circuit **27** (hereinafter, referred to as an LC resonance circuit **27**) composed of a reactor **27a** and a capacitor **27b** is connected to an AC output line between the semiconductor switching devices **11a** to **11d** and the transformer **12**. The other configurations are the same as those shown in FIG. **11** in the above embodiment 1.

First, zero-current switching operation will be described with reference to a waveform diagram of each section shown in FIG. **23**.

When the semiconductor switching devices **11a** and **11d** are both ON, and when the semiconductor switching devices **11b** and **11c** are both ON, a current of sine wave as shown in FIG. **23** flows on the primary side of the transformer **12**, owing to LC resonance effect of the LC resonance circuit **27**. The ON/OFF timings of the semiconductor switching devices **11a** and **11d** and the semiconductor switching devices **11b** and **11c** are synchronized with the zero cross phase of the current wave, whereby zero-current switching can be realized. After a positive current flows while the semiconductor switching devices **11a** and **11d** are both ON, the semiconductor switching devices **11a** and **11d** are turned from on to off, and then the semiconductor switching devices **11b** and **11c** are turned on. Then, this time, a negative current flows.

Also in the present embodiment, as in the above embodiment 1, the control circuit **16** controls the high-power-factor converter section **100** as shown in FIGS. **6(a)** and **6(b)**. In addition, as shown in FIG. **8** or **12**, the control circuit **16** outputs the drive signal **30c** (**30ca** and **30cb**) as the duty instruction for driving the semiconductor switching devices **11a** and **11d** and the semiconductor switching devices **11b** and **11c** such that the output voltage  $V_{out}$  or the output current  $I_{out}$  as a DC output follows an instruction value, thereby controlling the DC/DC converter section **200a**. Then, as shown in FIG. **10**, the control circuit **16** performs feedback control such that the difference between a predetermined duty set value and the generated duty instruction approaches zero, thereby adjusting the target voltage  $V_{dc}^*$  of the smoothing capacitor **10**. It is noted that in FIG. **23**, a first drive signal is the drive signal **30ca** for the semiconductor switching devices **11a** and **11d**, and a second drive signal is the drive signal **30cb** for the semiconductor switching devices **11b** and **11c**. In addition, the duty set value in this case is a value that can realize zero-current switching of the semiconductor switching devices **11a** to **11d**.

In zero-current switching of the semiconductor switching devices **11a** to **11d**, the switching frequency and the output voltage are determined by the turns ratio of the transformer **12** and the constant of the LC resonance circuit **27**. For changing the output voltage, as shown in FIG. **24(a)**, if the ON-time, that is, the duty ratio of each of the semiconductor switching devices **11a** to **11d** is changed to decrease the output voltage, the switching timing of each of the semiconductor switching devices **11a** to **11d** shifts from the current zero point. As a result, zero-current switching is not realized.

In the present embodiment, the duty set value is determined so as to realize the zero-current switching, and the target voltage  $V_{dc}^*$  of the smoothing capacitor **10** is adjusted in accordance with the DC output to the load **2**. Thus, as shown

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in FIG. 24(b), it becomes possible to reduce the output voltage while realizing zero-current switching.

Therefore, since the output voltage can be made variable while zero-current switching of the semiconductor switching devices 11a to 11d is maintained, it is possible to significantly reduce switching loss, thereby reducing power loss of the power conversion apparatus and improving the power conversion efficiency.

It is noted that such switching as described in the above embodiments 2 to 4 that makes loss of switching of the semiconductor switching devices 11a to 11d substantially zero or very small, is referred to as soft switching. In the above embodiments 2 to 4, the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is adjusted so as to allow the semiconductor switching devices 11a to 11d to perform soft switching.

#### Embodiment 5

Next, embodiment 5 of the present invention will be described.

In the power conversion apparatus of the above embodiments 1 to 4, the primary side and the secondary side are insulated from each other by the transformer 12 in the DC/DC converter section. In the present embodiment, the case of applying a non-insulation circuit will be described. FIG. 25 is a diagram showing the circuit configuration of a power conversion apparatus according to embodiment 5 of the present invention. As shown in FIG. 25, a DC/DC converter section 200c is composed of a general step-down chopper comprising a semiconductor switching device 28, a diode 29, the reactor 14 for smoothing, and the capacitor 15 for smoothing.

A control circuit 16c outputs the drive signals 30a and 30b for the semiconductor switching devices 5a and 5b and the short-circuit switch 8 in the high-power-factor converter section 100, and a drive signal 30d as a duty instruction for the semiconductor switching device 28 in the DC/DC converter section 200c.

The other configurations are the same as those shown in FIG. 11 in the above embodiment 1.

Also in the present embodiment, as in the above embodiment 1, as shown in FIG. 10, feedback control is performed such that the difference between a predetermined duty set value and the generated duty instruction approaches zero, thereby adjusting the target voltage  $V_{dc}^*$  of the smoothing capacitor 10. In addition, the high-power-factor converter section 100 is controlled as shown in FIGS. 6(a) and 6(b), and the drive signal 30d as a duty instruction for driving the semiconductor switching device 28 is outputted such that the output voltage  $V_{out}$  as a DC output follows the output voltage instruction value  $V_{out}^*$  as shown in FIG. 8, thereby controlling the DC/DC converter section 200c.

Thus, in accordance with the output voltage  $V_{out}$  of the DC/DC converter section 200c which is a DC output to the load 2, the control circuit 16c adjusts the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 such that the duty ratio of the semiconductor switching device 28 of the DC/DC converter section 200c approaches the duty set value, thereby controlling the high-power-factor converter section 100 and the DC/DC converter section 200c. If the duty ratio that allows the DC/DC converter section 200c to operate in an optimum condition that decreases loss is used as the duty set value, the effect of reducing power loss, improving power conversion efficiency, and reducing the size of the apparatus, can be provided as in the above embodiment 1.

In addition, since the current increase gradient of the reactor 14 for smoothing can be controlled to be substantially

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constant regardless of the magnitude of the output voltage  $V_{out}$ , it becomes possible to reduce the size of the reactor 14 for smoothing.

Also in this case, the original target voltage  $V_{dc}^*$  of the smoothing capacitor 10 when the voltage instruction value  $V_{out}^*$  is to be changed may be determined so as to optimize the duty ratio of the semiconductor switching device 28.

Further, even if the control for adjusting the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 in accordance with the output voltage  $V_{out}$  is omitted, since the target voltage  $V_{dc}^*$  is determined in accordance with the voltage instruction value  $V_{out}^*$ , the effect of reducing power loss and reducing the size of the apparatus can be provided.

For example, when the duty ratio of the semiconductor switching device 28 is 100%, the semiconductor switching device 28 is always ON, and if voltage drop in the semiconductor switching device 28 and the reactor 14 for smoothing is ignored, the output voltage  $V_{out}$  of the DC/DC converter section 200c is equal to the input voltage  $V_{dc}$  (the voltage of the smoothing capacitor 10). Therefore, if the target voltage  $V_{dc}^*$  of the smoothing capacitor 10 is set as  $V_{dc}^* = V_{out}^*$ , the duty ratio of the semiconductor switching device 28 becomes 100%, whereby switching loss does not occur in the semiconductor switching device 28.

However, the range in which the voltage  $V_{dc}$  of the smoothing capacitor 10 for output in the high-power-factor converter section 100 is variable is determined by the voltage  $V_{in}$  of the AC voltage source 1. Therefore, if the output voltage  $V_{out}^*$  is equal to or lower than the lower limit value of the range in which the voltage  $V_{dc}$  of the smoothing capacitor 10 is variable, the high-power-factor converter section 100 sets  $V_{dc}^*$  at the lower limit value of the range in which the voltage  $V_{dc}$  of the smoothing capacitor 10 is variable, and then, for the remaining difference, the voltage  $V_{out}$  of the capacitor 15 is caused to follow the voltage instruction value  $V_{out}^*$  by duty control for the semiconductor switch 28 of the DC/DC converter section 200c.

Such control may be performed by synchronized rectification, using a MOSFET, instead of the diode 29 of the DC/DC converter section 200c.

Although the case where the DC/DC converter section 200c is a general step-down chopper has been described, the circuit configuration is not limited thereto. Another non-insulation type DC/DC converter such as a step-up chopper or a step-up/down chopper may be used.

The invention claimed is:

1. A power conversion apparatus comprising:

an AC/DC converter which converts an AC voltage to a DC voltage;

a smoothing capacitor connected to the DC side of the AC/DC converter;

a DC/DC converter, comprising a semiconductor switch, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs the resultant power to a load; and

a controller which controls the AC/DC converter such that a power factor of AC is controlled and the DC voltage of the AC/DC converter follows a DC voltage target value, and which controls the DC/DC converter by controlling a duty ratio of the semiconductor switch such that a DC input/output between the DC/DC converter and the load follows an instruction value, wherein

the controller adjusts the DC voltage target value of the AC/DC converter such that the duty ratio of the semiconductor switch of the DC/DC converter approaches a set value.

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2. The power conversion apparatus according to claim 1, wherein

the controller generates a duty instruction for the semiconductor switch such that a voltage or a current as the DC input/output between the DC/DC converter and the load follows the instruction value, thereby performing duty control for the semiconductor switch based on the duty instruction, and generates the DC voltage target value of the AC/DC converter such that the duty instruction approaches the set value, thereby controlling the AC/DC converter.

3. The power conversion apparatus according to claim 1, wherein

the DC/DC converter comprises:  
a transformer that is insulated;  
a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting a DC voltage of the smoothing capacitor to an AC voltage; and  
a rectification circuit connected to the other end of the transformer.

4. The power conversion apparatus according to claim 1, wherein

the DC/DC converter is configured so that the semiconductor switch performs soft switching, and  
the controller adjusts the DC voltage target value so that the semiconductor switch of the DC/DC converter to perform performs soft switching, and controls the DC/DC converter by using soft switching of the semiconductor switch.

5. The power conversion apparatus according to claim 4, wherein

the DC/DC converter comprises:  
a transformer that is insulated;  
a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting the DC voltage of the smoothing capacitor to an AC voltage; and  
a rectification circuit connected to the other end of the transformer,

the converter comprises:

a capacitor connected in parallel to each of the semiconductor switches; and  
a reactor connected to an AC line, and

the controller adjusts the DC voltage target value of the AC/DC converter so that the plurality of semiconductor switches in the DC/DC converter to perform zero-voltage switching.

6. The power conversion apparatus according to claim 4, wherein:

the DC/DC converter comprises:  
a transformer that is insulated;  
a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting a DC voltage of the smoothing capacitor to an AC voltage; and  
a rectification circuit connected to the other end of the transformer, the converter comprises:

a capacitor connected in parallel to each of the semiconductor switches; and  
a reactor connected to an AC line, and wherein  
the controller controls the plurality of semiconductor switches of the DC/DC converter by using zero-voltage switching, and

the controller decreases the DC voltage target value of the AC/DC converter so as to increase the current in the

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reactor, and increases the DC voltage target value of the AC/DC converter so as to decrease the current in the reactor.

7. The power conversion apparatus according to claim 1, wherein

the AC/DC converter comprises:

an inverter circuit including one or more single-phase inverters whose AC sides are connected in series and each of which includes a plurality of semiconductor switches and a DC voltage source, the inverter circuit superimposing the sum of output voltages of the single-phase inverters onto the AC voltage; and  
a bridge circuit having a switch and connected to the inverter circuit.

8. The power conversion apparatus according to claim 7, wherein

the controller controls the bridge circuit such that the voltage of the DC voltage source of the inverter circuit follows an instruction value, and controls the inverter circuit by using a current instruction such that the DC voltage of the AC/DC converter follows the DC voltage target value.

9. The power conversion apparatus according to claim 1, wherein:

the AC/DC converter comprises a plurality of semiconductor switches, and

the controller controls the plurality of semiconductor switches of the AC/DC converter and the semiconductor switch of the DC/DC converter such that switching frequencies thereof are different from each other.

10. A power conversion apparatus, comprising:

an AC/DC converter which converts an AC voltage to a DC voltage;

a smoothing capacitor connected to the DC side of the AC/DC converter;

a DC/DC converter, comprising a semiconductor switch, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs the resultant power to a load; and

a controller which controls the AC/DC converter such that a power factor of AC is controlled and the DC voltage of the AC/DC converter follows a DC voltage target value, and which controls the DC/DC converter by duty control for the semiconductor switch such that a DC input/output between the DC/DC converter and the load follows an instruction value,

wherein the controller determines the DC voltage target value of the AC/DC converter, based on the instruction value of the DC input/output between the DC/DC converter and the load, so as to optimize the duty ratio of the semiconductor switch of the DC/DC converter.

11. The power conversion apparatus according to claim 10, wherein

the DC/DC converter comprises:

a transformer that is insulated;  
a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting the DC voltage of the smoothing capacitor to an AC voltage; and  
a rectification circuit connected to the other end of the transformer.

12. The power conversion apparatus according to claim 10, wherein

the DC/DC converter is configured so that the semiconductor switch performs soft switching, and

the controller adjusts the DC voltage target value so that the semiconductor switch of the DC/DC converter performs

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soft switching, and controls the DC/DC converter by using soft switching of the semiconductor switch.

13. The power conversion apparatus according to claim 10, wherein

the AC/DC converter comprises:

an inverter circuit including one or more single-phase inverters whose AC sides are connected in series and each of which includes a plurality of semiconductor switches and a DC voltage source, the inverter circuit superimposing the sum of output voltages of the single-phase inverters onto the AC voltage; and a bridge circuit having a switch and connected to the inverter circuit.

14. The power conversion apparatus according to claim 13, wherein

the controller controls the bridge circuit such that the voltage of the DC voltage source of the inverter circuit follows an instruction value, and controls the inverter circuit by using a current instruction such that the DC voltage of the AC/DC converter follows the DC voltage target value.

15. The power conversion apparatus according to claim 10, wherein:

the AC/DC converter comprises a plurality of semiconductor switches, and

the controller controls the plurality of semiconductor switches of the AC/DC converter and the semiconductor switch of the DC/DC converter such that switching frequencies thereof are different from each other.

16. A power conversion apparatus, comprising:

an AC/DC converter which converts an AC voltage to a DC voltage;

a smoothing capacitor connected to the DC side of the AC/DC converter;

a DC/DC converter, comprising a semiconductor switch, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs a resultant power to a load; and

a controller which controls the AC/DC converter such that a power factor of AC is controlled and the DC voltage of the AC/DC converter follows a DC voltage target value, and which controls the DC/DC converter by duty control for the semiconductor switch such that a DC input/output between the DC/DC converter and the load follows an instruction value, wherein:

the controller adjusts the DC voltage target value of the AC/DC converter so that the semiconductor switch in the DC/DC converter performs soft switching,

the DC/DC converter comprises:

a transformer that is insulated;

a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting a DC voltage of the smoothing capacitor to an AC voltage; and

a rectification circuit connected to the other end of the transformer,

the converter comprises a series circuit, including a reactor and a capacitor, which is connected to an AC line, and

the controller adjusts the DC voltage target value of the AC/DC converter so that the plurality of semiconductor switches in the DC/DC converter perform zero-current switching, and

the controller determines a set value of the duty ratio of the plurality of semiconductor switches so that the plurality

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of semiconductor switches of the DC/DC converter to perform zero-current switching, and adjusts the DC voltage target value of the AC/DC converter such that the duty ratio of the plurality of semiconductor switches approaches the set value.

17. A power conversion apparatus, comprising:

an AC/DC converter which converts an AC voltage to a DC voltage;

a smoothing capacitor connected to the DC side of the AC/DC converter;

a DC/DC converter, comprising a semiconductor switch, which performs DC/DC conversion for DC power of the smoothing capacitor and outputs a resultant power to a load; and

a controller which controls the AC/DC converter such that a power factor of AC is controlled and the DC voltage of the AC/DC converter follows a DC voltage target value, and which controls the DC/DC converter by duty control for the semiconductor switch such that a DC input/output between the DC/DC converter and the load follows an instruction value, wherein:

the controller adjusts the DC voltage target value of the AC/DC converter so that the semiconductor switch in the DC/DC converter performs soft switching,

wherein

the AC/DC converter comprises:

an inverter circuit including one or more single-phase inverters whose AC sides are connected in series and each of which includes a plurality of semiconductor switches and a DC voltage source, the inverter circuit superimposing the sum of output voltages of the single-phase inverters onto the AC voltage; and

a bridge circuit having a switch and connected to the inverter circuit,

the controller controls the bridge circuit such that the voltage of the DC voltage source of the inverter circuit follows an instruction value, and controls the inverter circuit by using a current instruction such that the DC voltage of the AC/DC converter follows the DC voltage target value.

18. The power conversion apparatus according to claim 17, wherein

the DC/DC converter comprises:

a transformer that is insulated;

a converter connected to one end of the transformer and having a plurality of the semiconductor switches, the converter converting a DC voltage of the smoothing capacitor to an AC voltage; and

a rectification circuit connected to the other end of the transformer, the converter comprises:

a capacitor connected in parallel to each of the semiconductor switches; and

a reactor connected to an AC line, and wherein

the controller controls the plurality of semiconductor switches of the DC/DC converter by using zero-voltage switching, and

the controller decreases the DC voltage target value of the AC/DC converter so as to increase the current in the reactor, and increases the DC voltage target value of the AC/DC converter so as to decrease the current in the reactor.

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